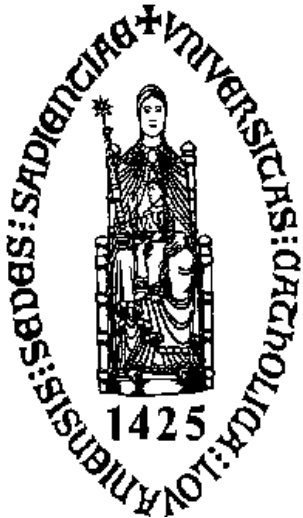


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# Bandgap and current reference circuits



**Willy Sansen**

**KULeuven, ESAT-MICAS**

**Leuven, Belgium**

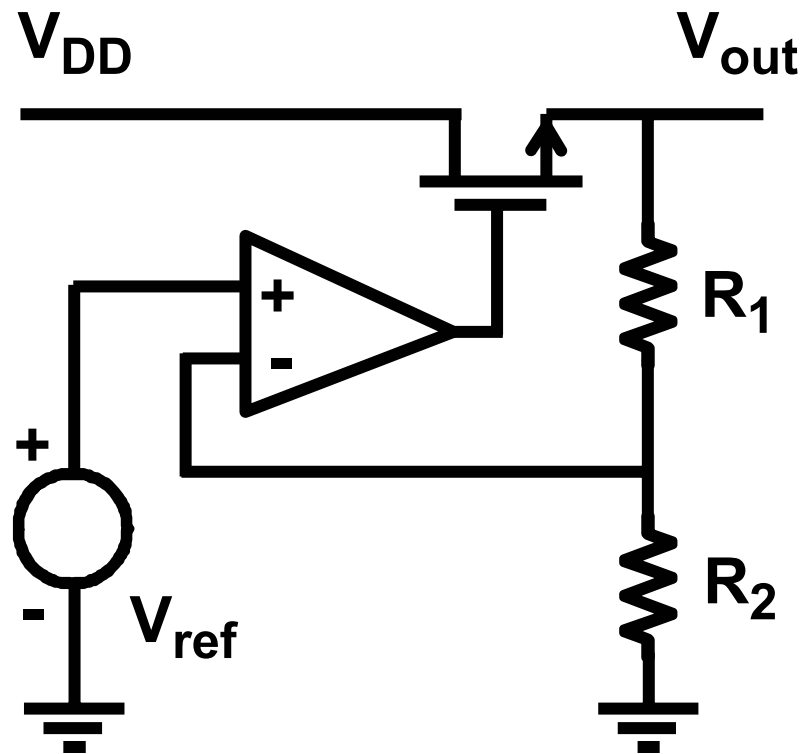
[willy.sansen@esat.kuleuven.be](mailto:willy.sansen@esat.kuleuven.be)



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# Voltage regulator

---

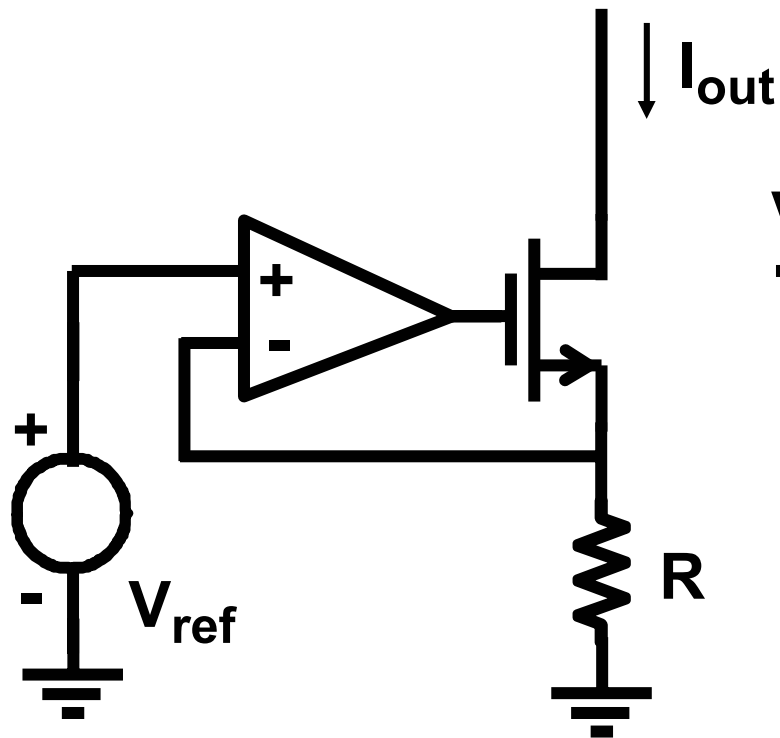


$$V_{out} = V_{ref} \frac{R_1 + R_2}{R_2}$$

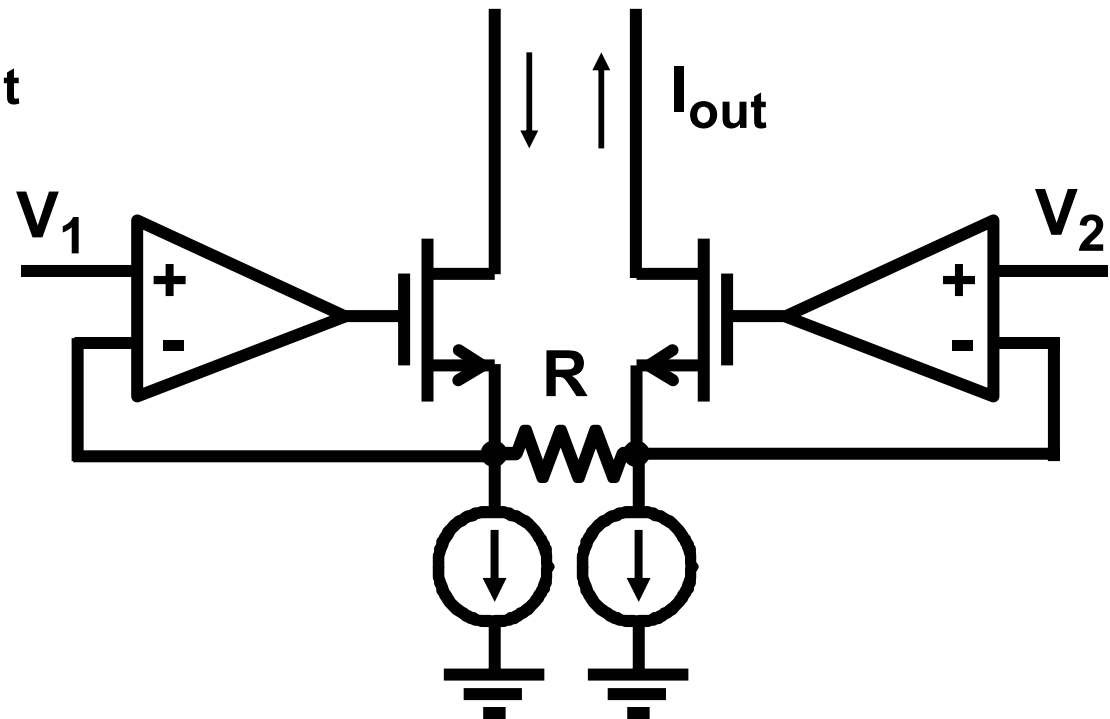
---

# Current regulator

---



$$I_{\text{out}} = \frac{V_{\text{ref}}}{R}$$



$$I_{\text{out}} = \frac{V_1 - V_2}{R}$$

---

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- **Principles**

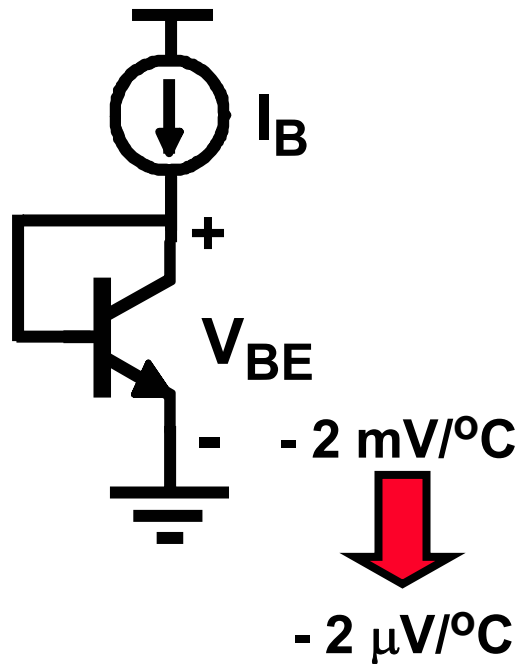
- Bipolar bandgap references
- CMOS bandgap references
- Bandgap references  $< 1\text{ V}$
- Current references
- LDO Regulators

Ref.: B.Gilbert, G.Meijer, ACD , Kluwer 1995

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# Bipolar transistor equations

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$$I_C = I_S \exp \left( \frac{V_{BE}}{kT/q} \right)$$

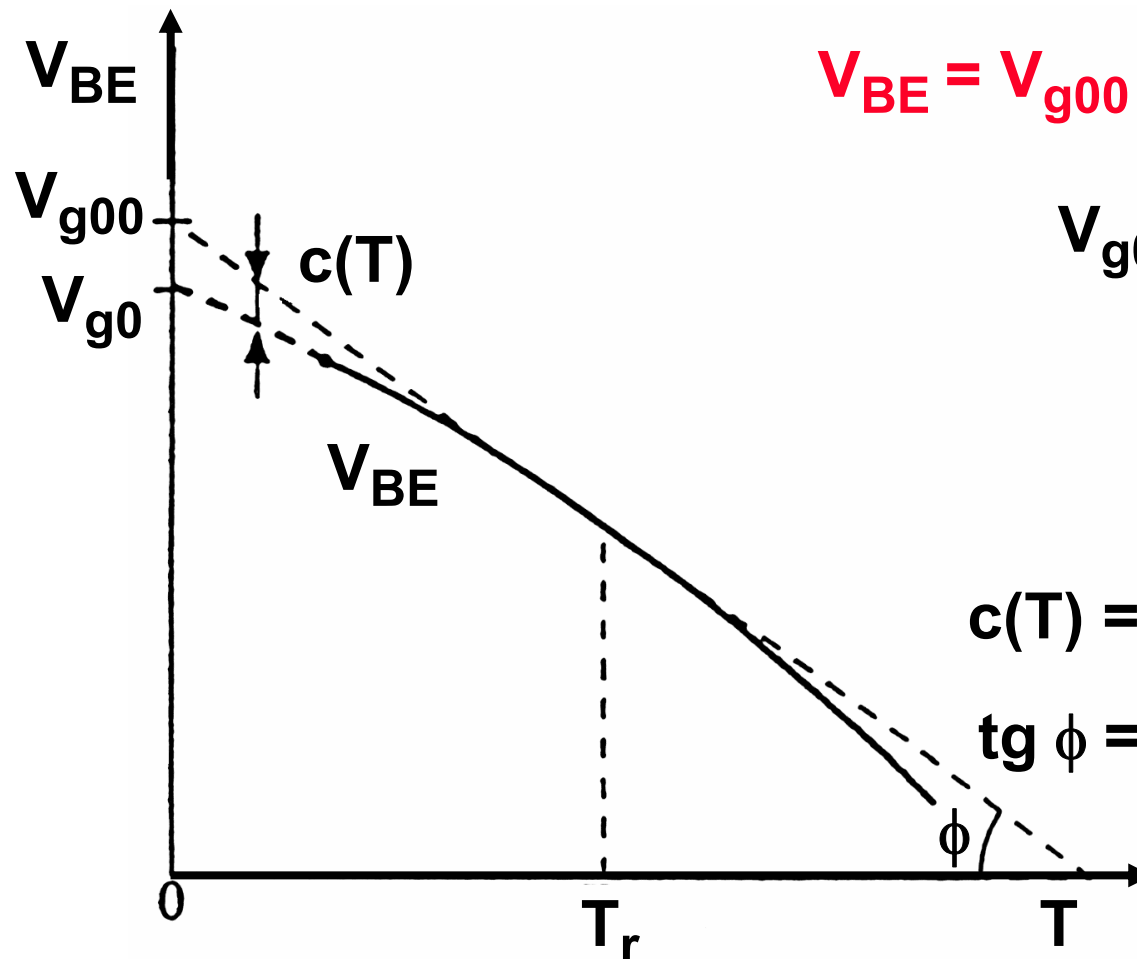
$$\text{or } I_C = CT^\eta \exp \left( \frac{V_{BE} - V_{g0}}{kT/q} \right)$$

$$\text{with } V_{g0} = 1268 \text{ mV} - \eta kT_r/q$$

$$\text{and } T_r = 323 \text{ K}$$

$$\text{which gives } V_{BE} = V_{g00} - \lambda T + c(T) \quad \text{for } I_C \sim T^m$$

# $V_{BE}$ versus Temperature



$$V_{BE} = V_{g00} - \lambda T + c(T) \text{ for } I_C \sim T^m$$

$$V_{g00} = V_{g0} + (\eta - m) k T_r / q$$

$$\lambda = \frac{V_{g00} - V_{BE}(T_r)}{T_r}$$

$$c(T) = (\eta - m) \frac{k}{q} \left( T - T_r - T \ln \frac{T}{T_r} \right)$$

$$\text{tg } \phi = \lambda$$

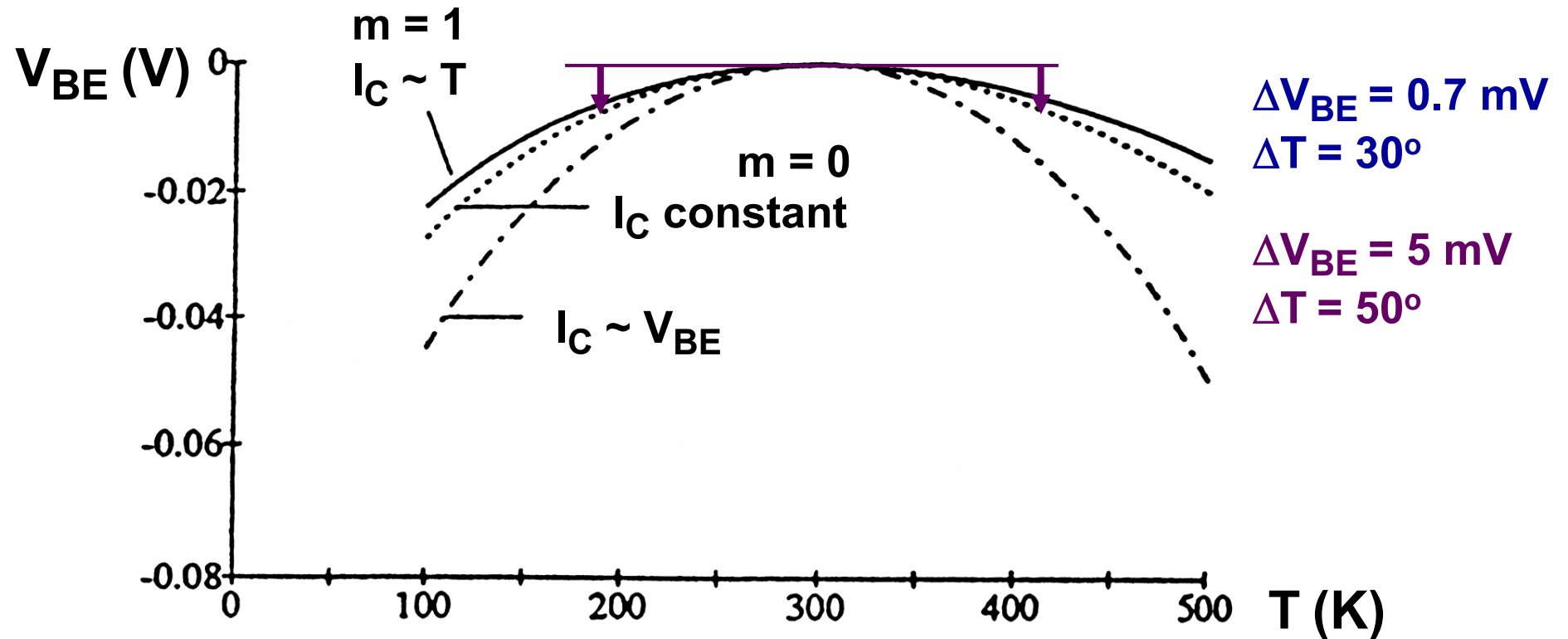
$$V_{g0} = 1156 \text{ mV}$$

$$\eta = 4$$

$$T_r = 300 \text{ K}$$

$$V_{BE}(T_r) = 700 \text{ mV}$$

# The curvature $c(T)$

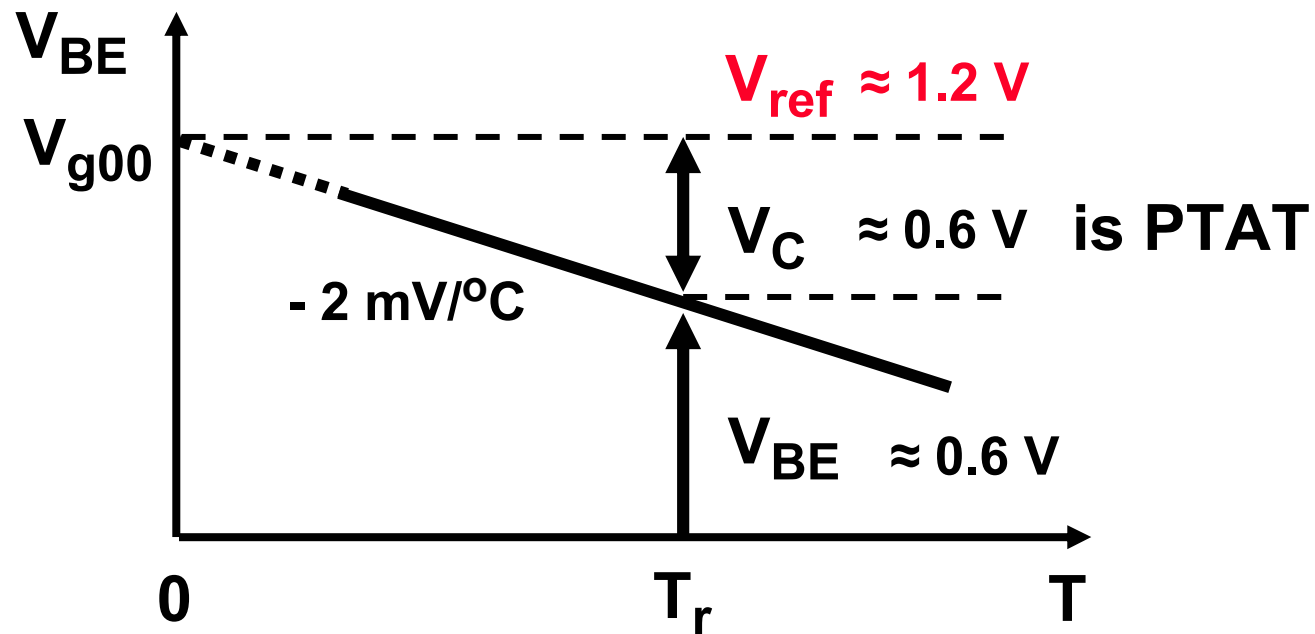


$m = 1$	$I_C \sim T$	$g_m$ constant
$m = 0$	$I_C$ constant	$g_m \sim T^{-1}$
$m = -$	$I_C \sim V_{BE}$	$g_m \sim T^{-x}$

---

# Bandgap reference $V_{ref}$

---



$$V_{ref} = V_{BE} + V_C \quad V_C \sim \frac{kT}{q}$$



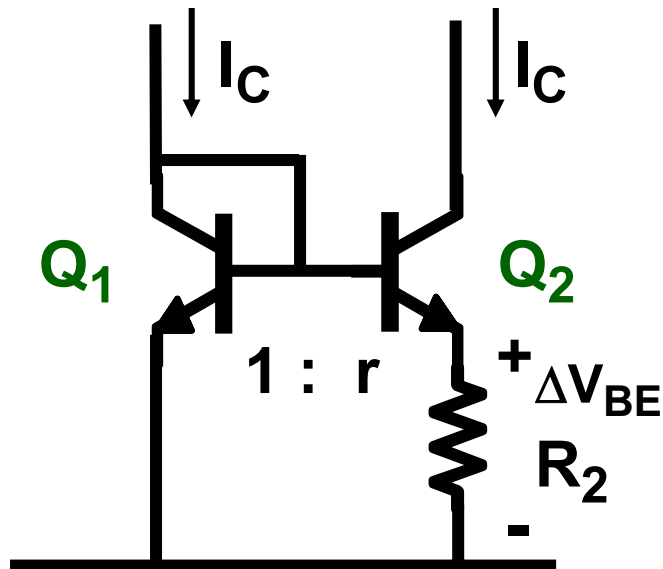
---

# PTAT voltage and current

---

$$I_C = I_S \exp \left( \frac{V_{BE}}{kT/q} \right) \quad V_{BE} = \frac{kT}{q} \ln \frac{I_C}{I_S}$$

$$\Delta V_{BE} = V_{BE1} - V_{BE2}$$



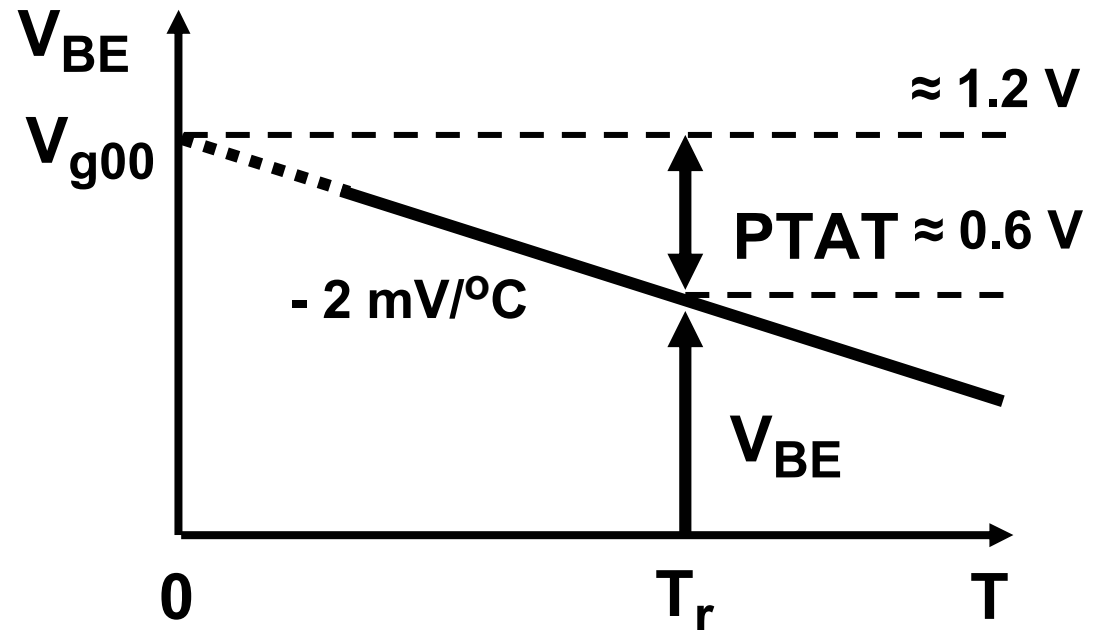
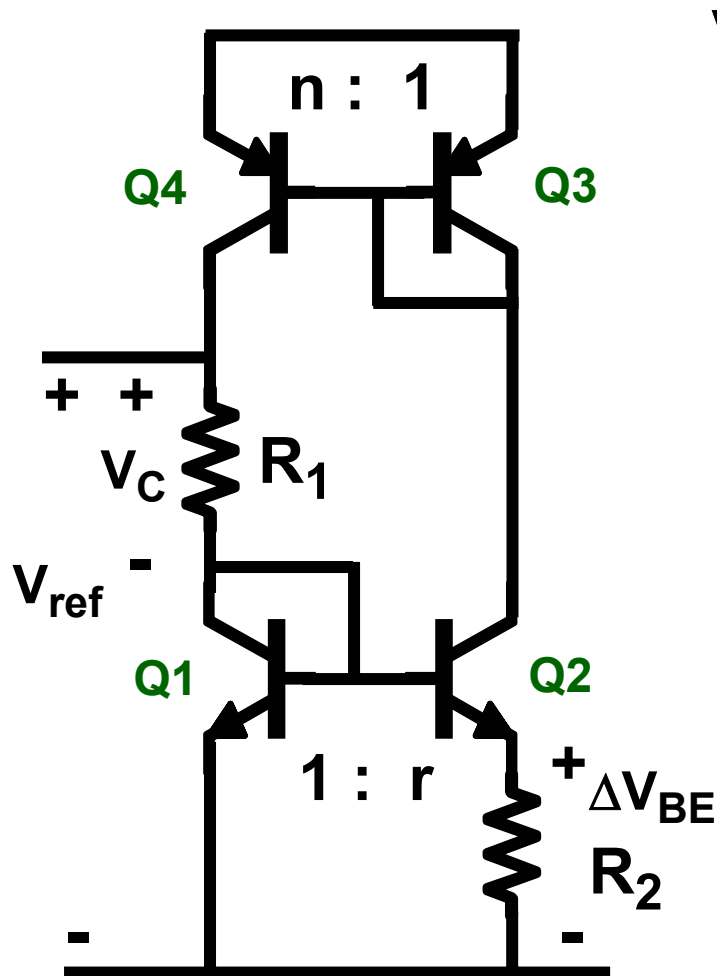
$$\Delta V_{BE} = \frac{kT}{q} \ln \frac{I_{S2}}{I_{S1}}$$

$$\Delta V_{BE} = \frac{kT}{q} \ln r$$

$$I_C = \frac{kT}{qR_2} \ln r$$

**$r$  is 10-1000 !!**

# Bandgap reference circuit



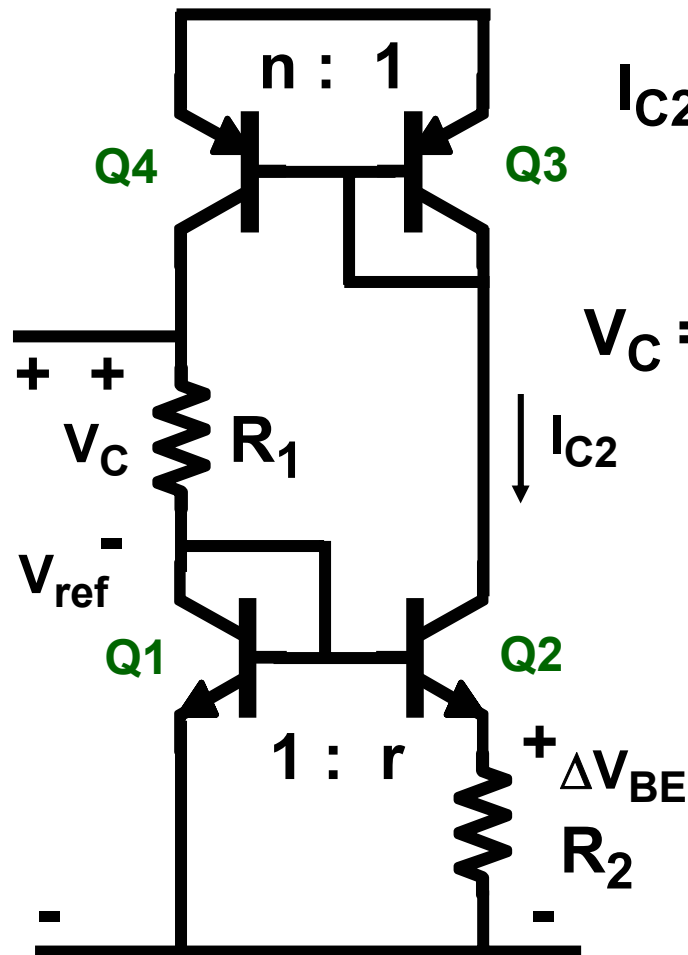
$$\Delta V_{BE} = \frac{kT}{q} \ln nr$$

$$I_{C2} = \frac{kT}{qR_2} \ln nr = \frac{A}{R_2}$$

$$V_{ref} = V_{BE} + V_C$$

$$V_C = n \frac{R_1}{R_2} \frac{kT}{q} \ln nr$$

# Noise Bandgap reference - 1



$$I_{C2} = \frac{kT}{qR_2} \ln nr = \frac{A}{R_2} \quad A = \frac{kT}{q} \ln nr \approx 0.12 \text{ V}$$

$$V_C = n \frac{R_1}{R_2} \frac{kT}{q} \ln nr = n \frac{R_1}{R_2} A = nR_1 I_{C2} \approx 0.6 \text{ V}$$

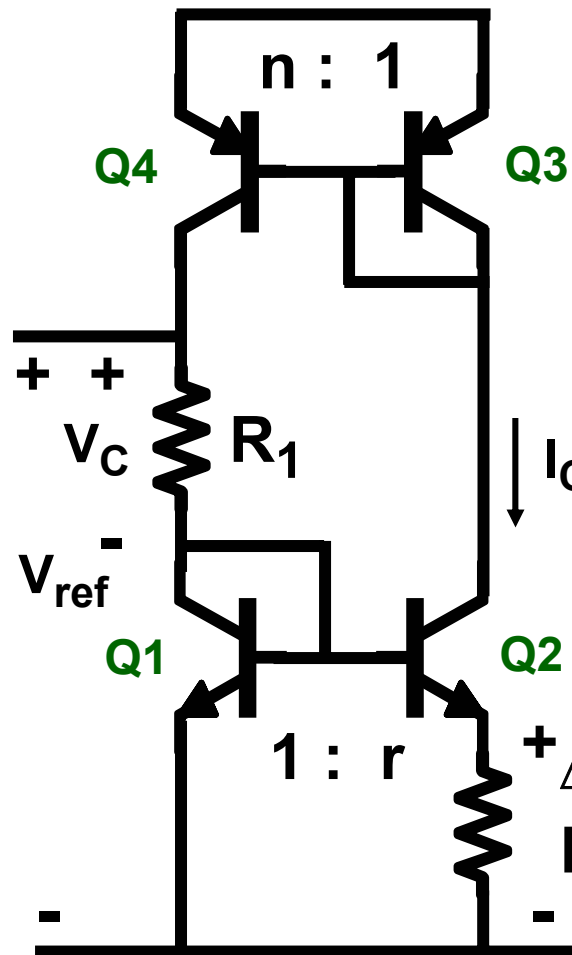
$$R_1 \gg 1/g_{m1} \quad R_1 I_{C1} \approx 0.5 \text{ V} \quad g_{m1} R_1 \approx 20$$

$$R_2 \gg 1/g_{m2} \quad R_2 I_{C2} \approx 0.06 \text{ V} \quad g_{m2} R_2 \approx 2.3$$

Noise sources :  $R_1$   $R_2$

$g_{m3,4}$  negligible for large  $V_{GS} - V_T$  or  $R_E$  !!

# Noise Bandgap reference - 2



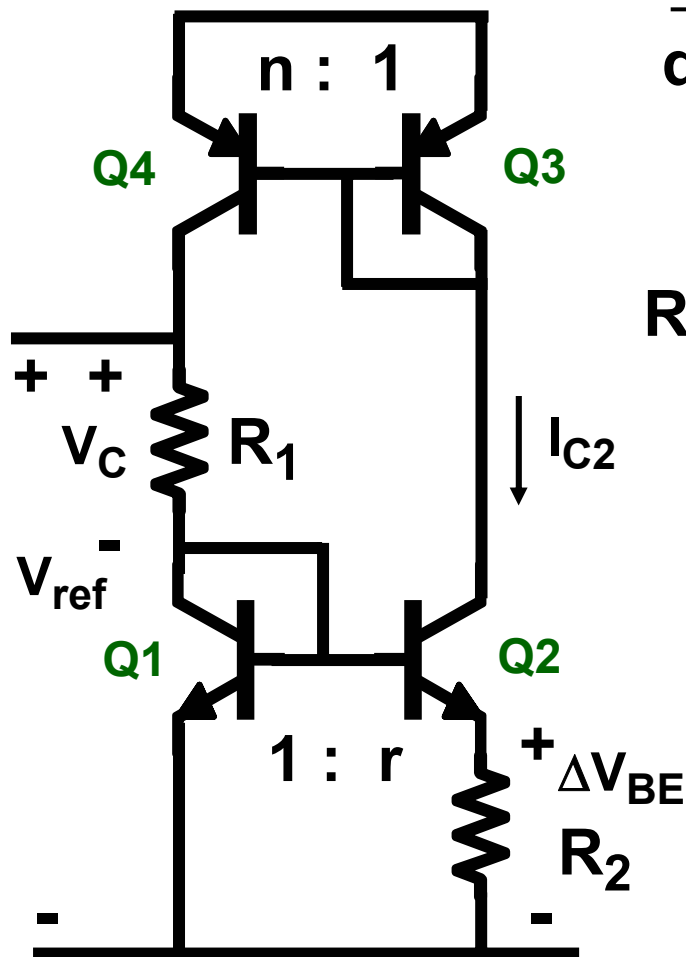
$$I_{C2} = \frac{kT}{qR_2} \ln nr = \frac{A}{R_2} \quad A = \frac{kT}{q} \ln nr \approx 0.12 \text{ V}$$

$$V_C = n \frac{R_1}{R_2} \frac{kT}{q} \ln nr = n \frac{R_1}{R_2} A = nR_1 I_{C2} \approx 0.6 \text{ V}$$

$$\begin{aligned} dV_{\text{Ref}}^2 &= 4kT R_1 df + R_1^2 n^2 \frac{4kT}{R_2} df \\ &= 4kT R_1 df \left( 1 + \frac{R_1}{R_2} n^2 \right) \end{aligned}$$

$$\frac{R_1}{R_2} n^2 = \frac{n}{R_2} R_1 n = \frac{n}{R_2} \frac{V_C}{I_{C2}} = \frac{nV_C}{\Delta V_{\text{BE}}} \gg 1$$

# Noise Bandgap reference - 3



$$\overline{dV_{\text{Ref}}^2} = 4kT R_1 \frac{R_1}{R_2} n^2 df$$

$$R_1 \frac{R_1}{R_2} n^2 = \frac{(R_1 n)^2}{R_2} = \frac{1}{R_2} \frac{V_C^2}{I_{C2}^2} = \frac{V_C^2}{I_{C2} \Delta V_{\text{BE}}}$$

$V_C \approx 0.6 \text{ V} :$

>> Large  $I_{C2}$  : small R's

>> Large  $r$  : large  $\Delta V_{\text{BE}}$

---

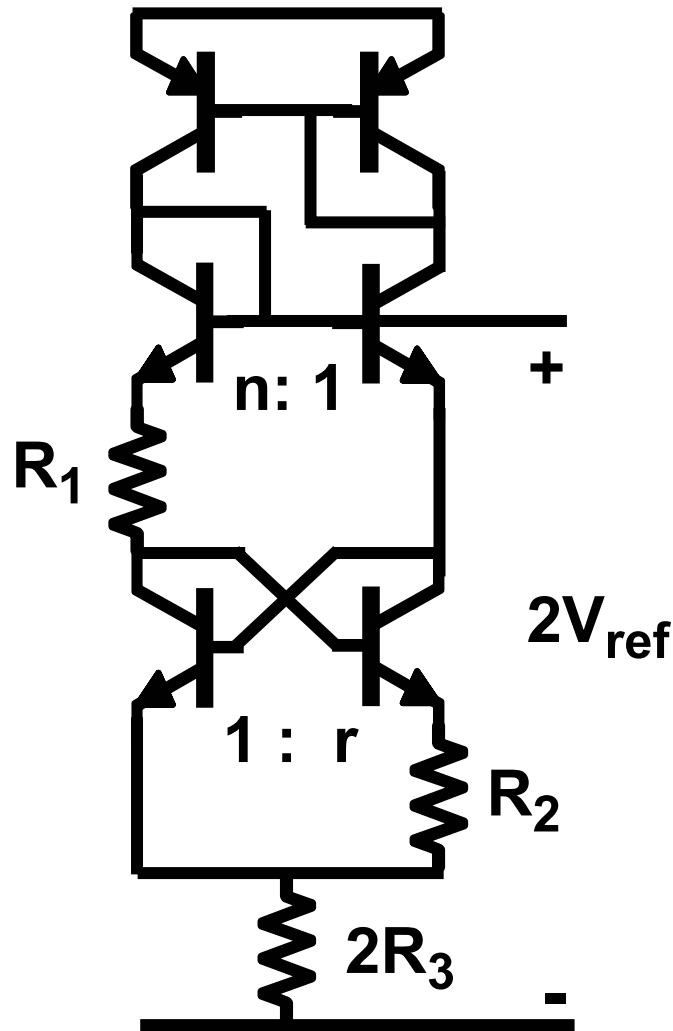
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- Current references
- LDO Regulators

Ref.: B. Gilbert, G.Meijer, ACD , Kluwer 1995

# Bandgap reference with bipolar transistors



Insensitive to  $\beta$  and  $V_E$  !

$$\Delta V_{BE} = \frac{kT}{q} \ln nr \quad I_C = \frac{kT}{qR_2} \ln nr$$

$$V_{ref} = 2V_{BE} + V_{R3}$$

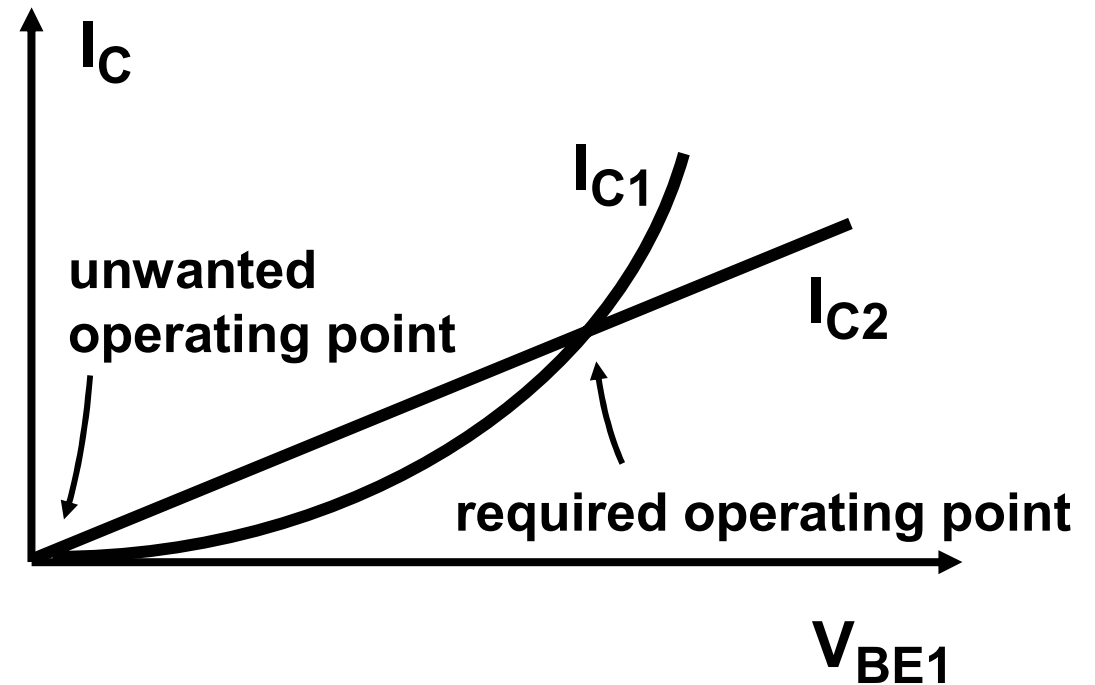
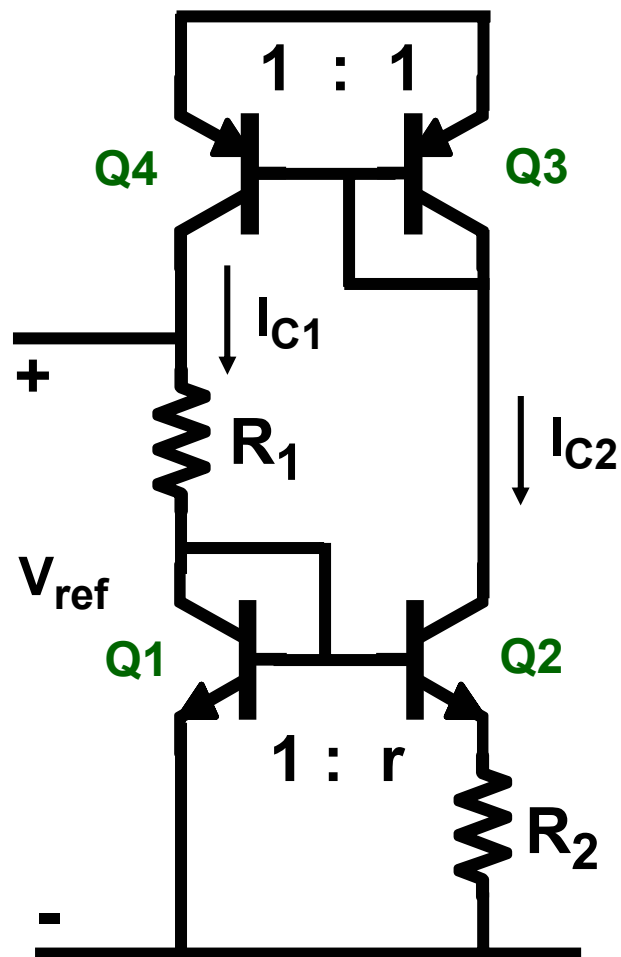
$$V_{R3} = 2R_3 \left( \frac{1}{R_1} + \frac{1}{R_2} \right) \frac{kT}{q} \ln nr$$

Ref.: G.Meijer, ACD , Kluwer 1995

---

# Start-up circuits required

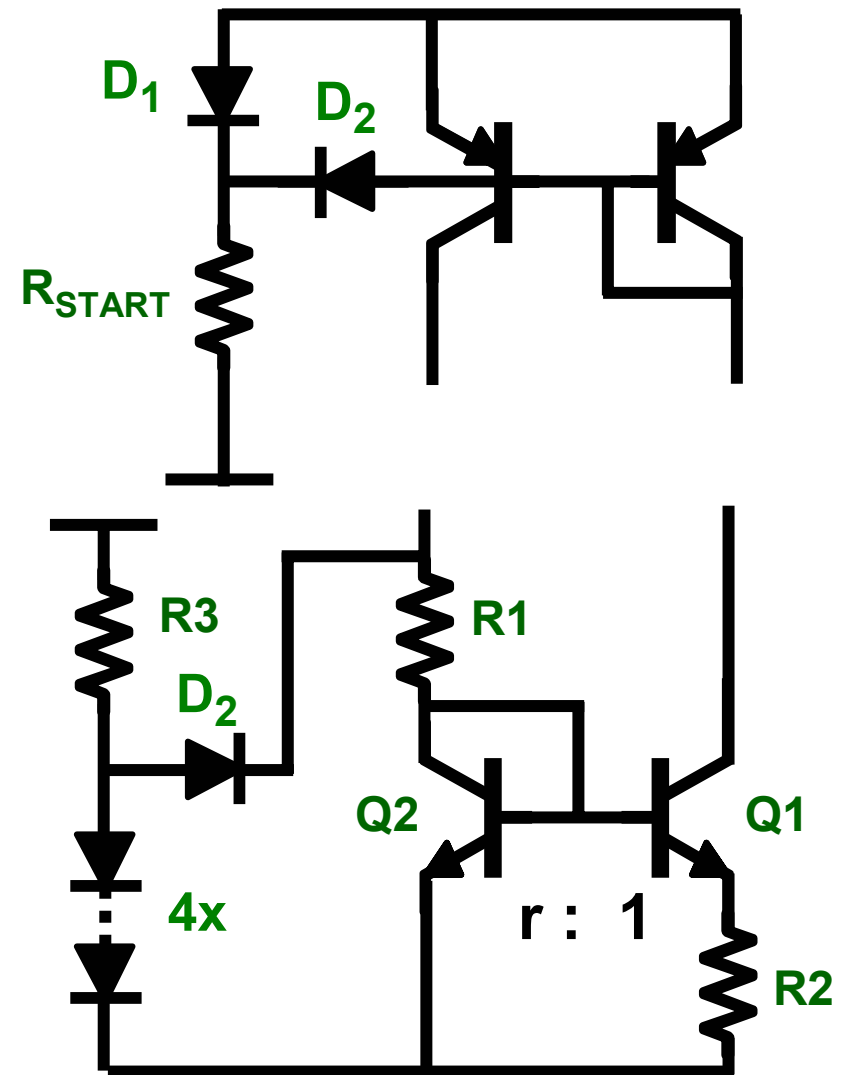
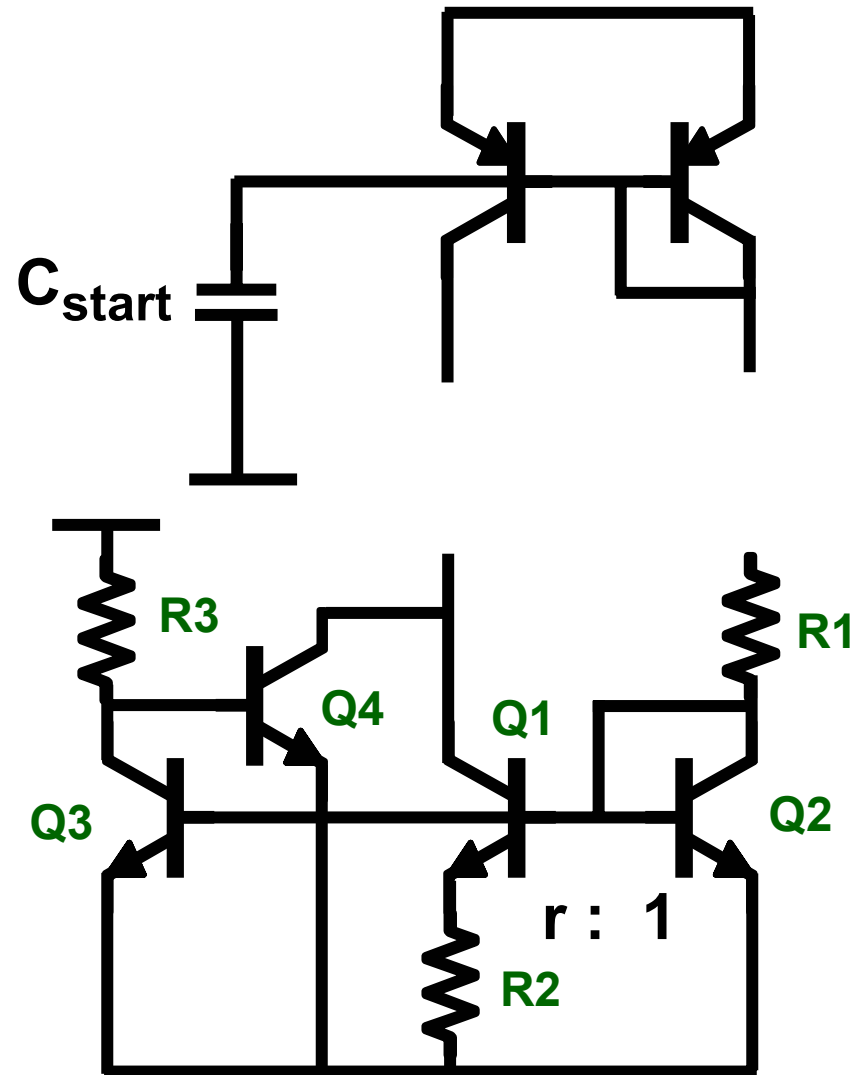
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$$V_{ref} = V_{BE1} + \frac{R_1}{R_2} \frac{kT}{q} \ln r$$



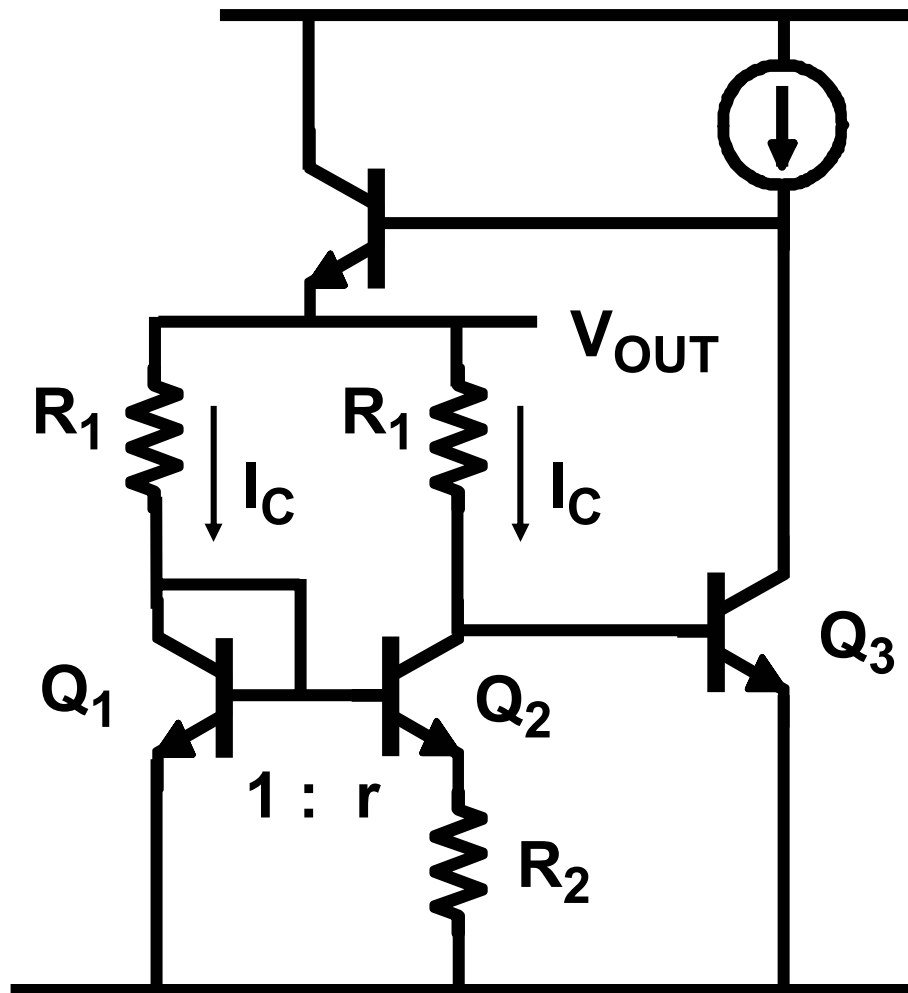
# Start-up circuits



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## Bipolar Bandgap reference without opamp

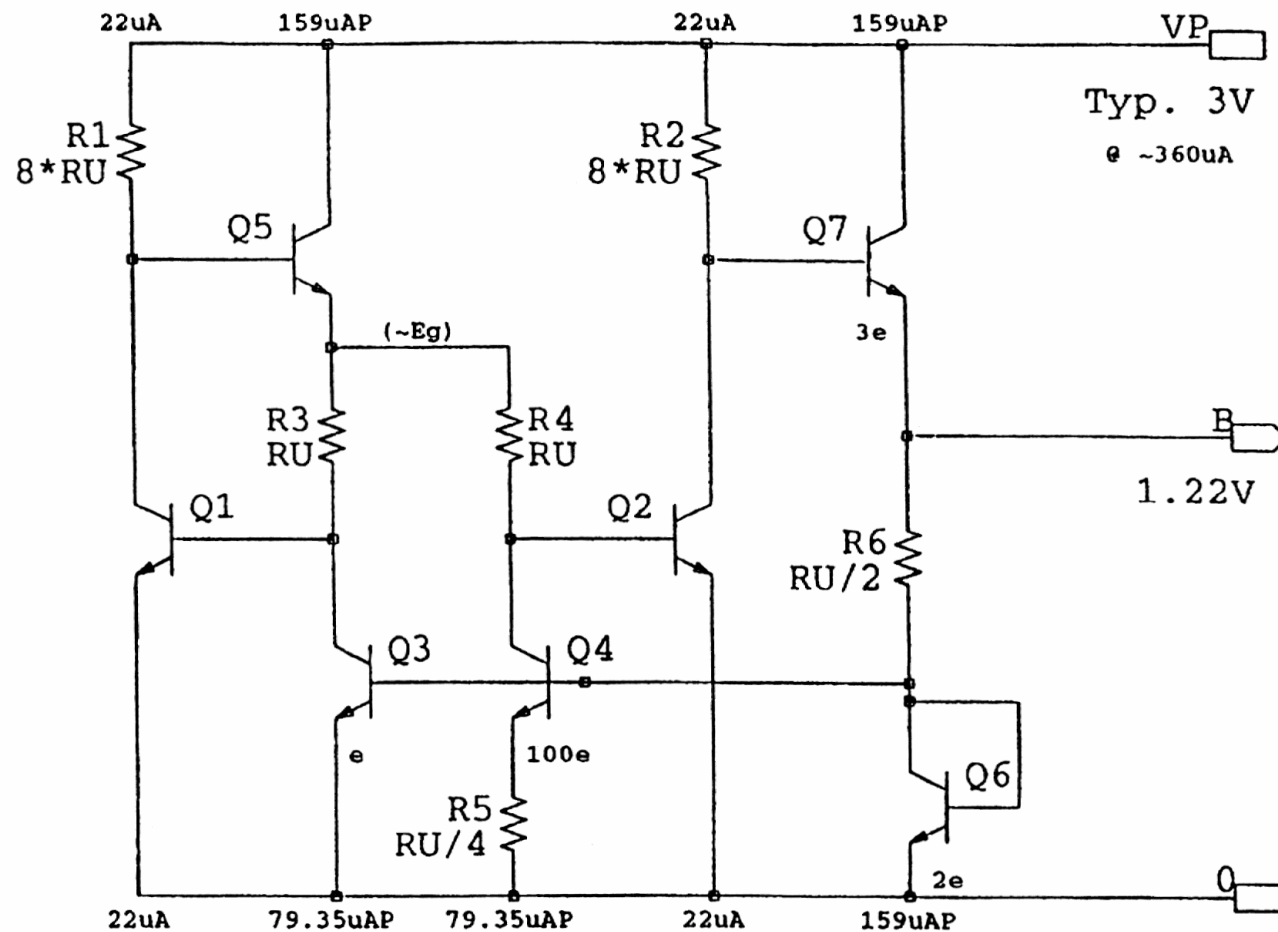
---



$$\begin{aligned} V_{OUT} &= V_{BE1} + R_1 I_C \\ &= V_{BE1} + \frac{R_1}{R_2} \frac{kT}{q} \ln r \end{aligned}$$

Ref. Widlar, JSSC Feb.1971, 2-7

## All NPN bipolar bandgap reference

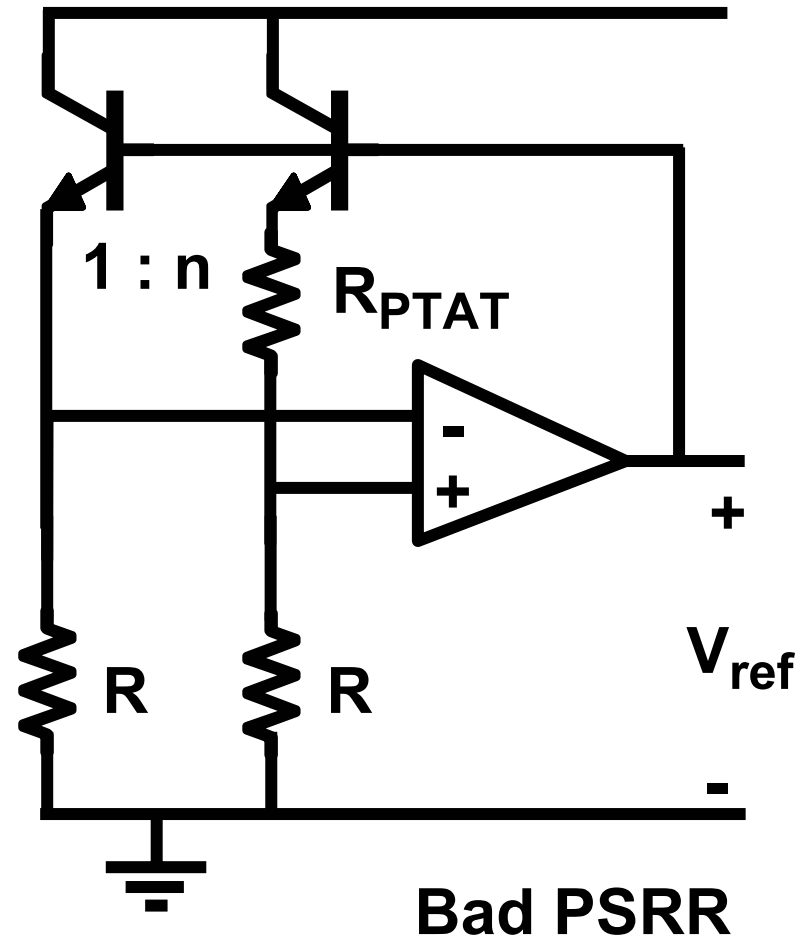
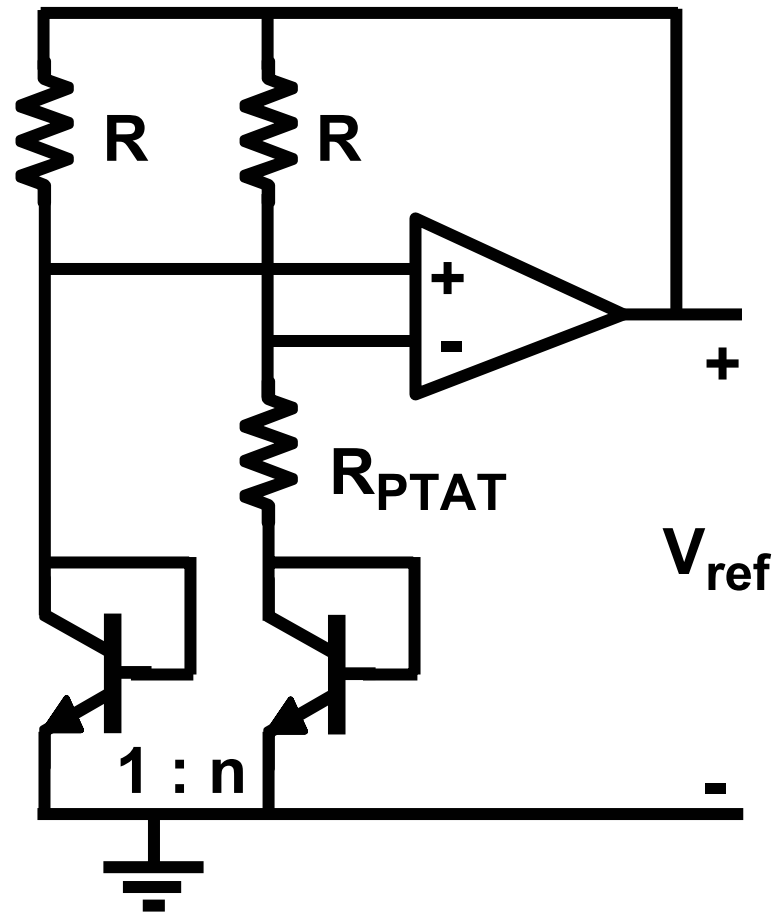


**Ref.: B.Gilbert, ACD , Kluwer 1995**

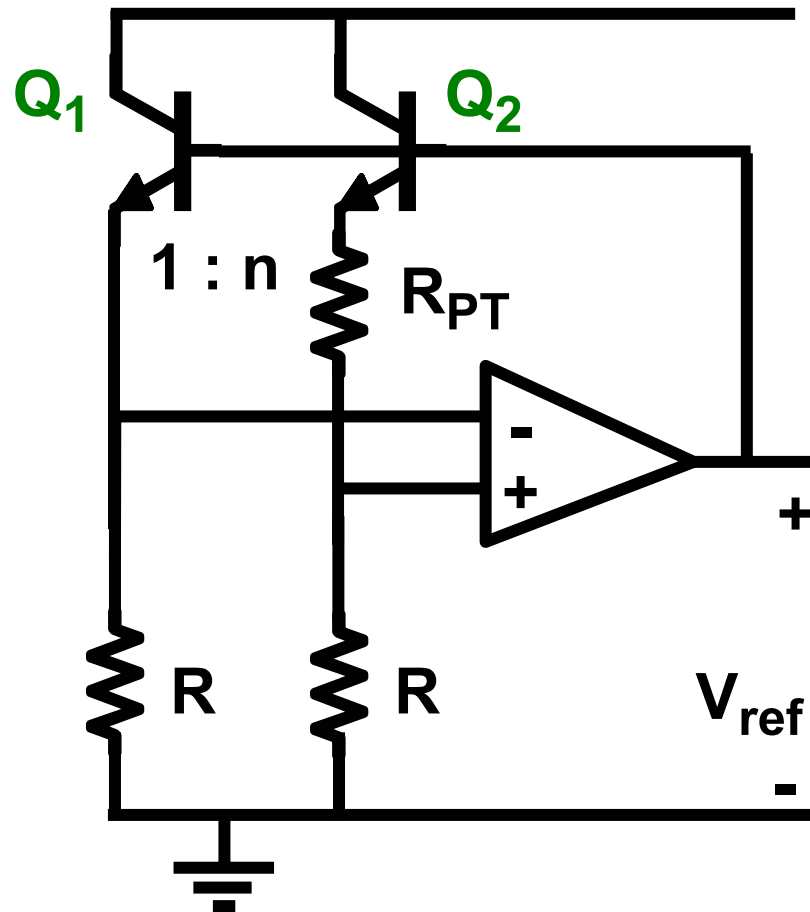
---

# Bipolar Bandgap references with opamps

---



# CMOS Bandgap ref.with opamp: error analysis 1



$$I_C = \frac{kT}{qR_{PT}} \ln n \quad A = \frac{R}{R_{PT}}$$

$$V_{ref} = V_{BE} + A (V_{BE1} - V_{BE2})$$

$$dV_{BE} = \frac{kT}{q} \left( \frac{dI_C}{I_C} - \frac{dI_S}{I_S} \right)$$

$$= \frac{kT}{q} \left( \frac{1}{\ln n} \frac{dn}{n} - \frac{dR_{PT}}{R_{PT}} - \frac{dI_S}{I_S} \right)$$

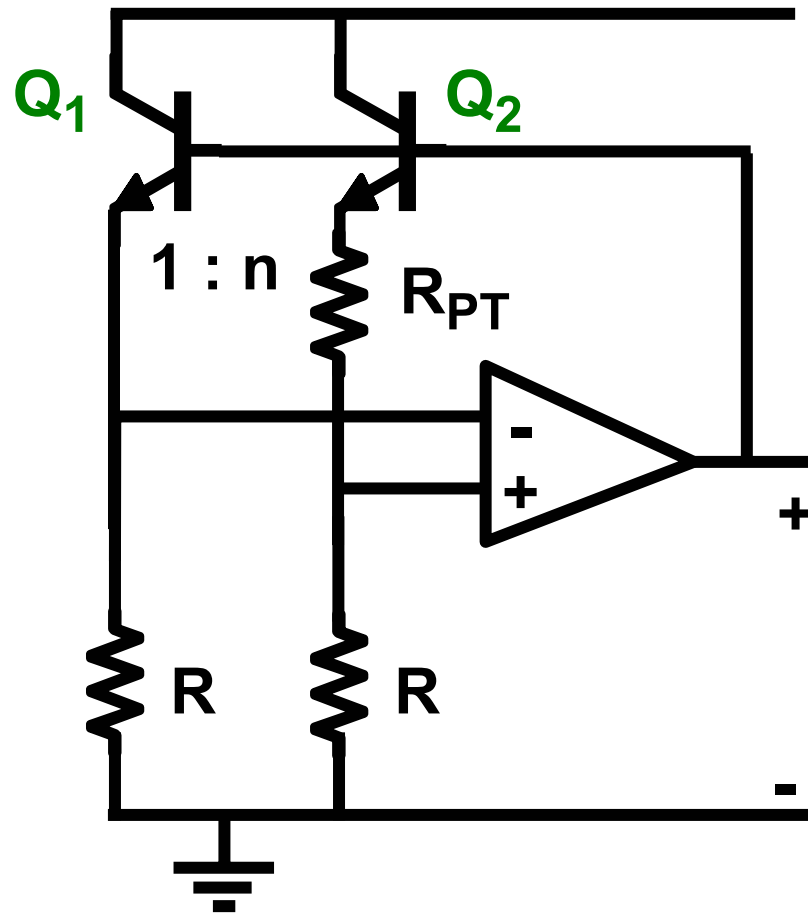
is PTAT !

$$= 26 \text{ mV} (0.46 \text{ } 2\% - 30\% - 20\%) \approx 13 \text{ mV (if } n = 10)$$

---

## CMOS Bandgap ref.with opamp: error analysis 2

---



$$V_{\text{ref}} = V_{\text{BE}} + A (V_{\text{BE1}} - V_{\text{BE2}})$$

$$V_{\text{BE1}} - V_{\text{BE2}} = \frac{kT}{q} \ln n$$

$$d(V_{\text{BE1}} - V_{\text{BE2}}) = \frac{kT}{q} \frac{dn}{n}$$

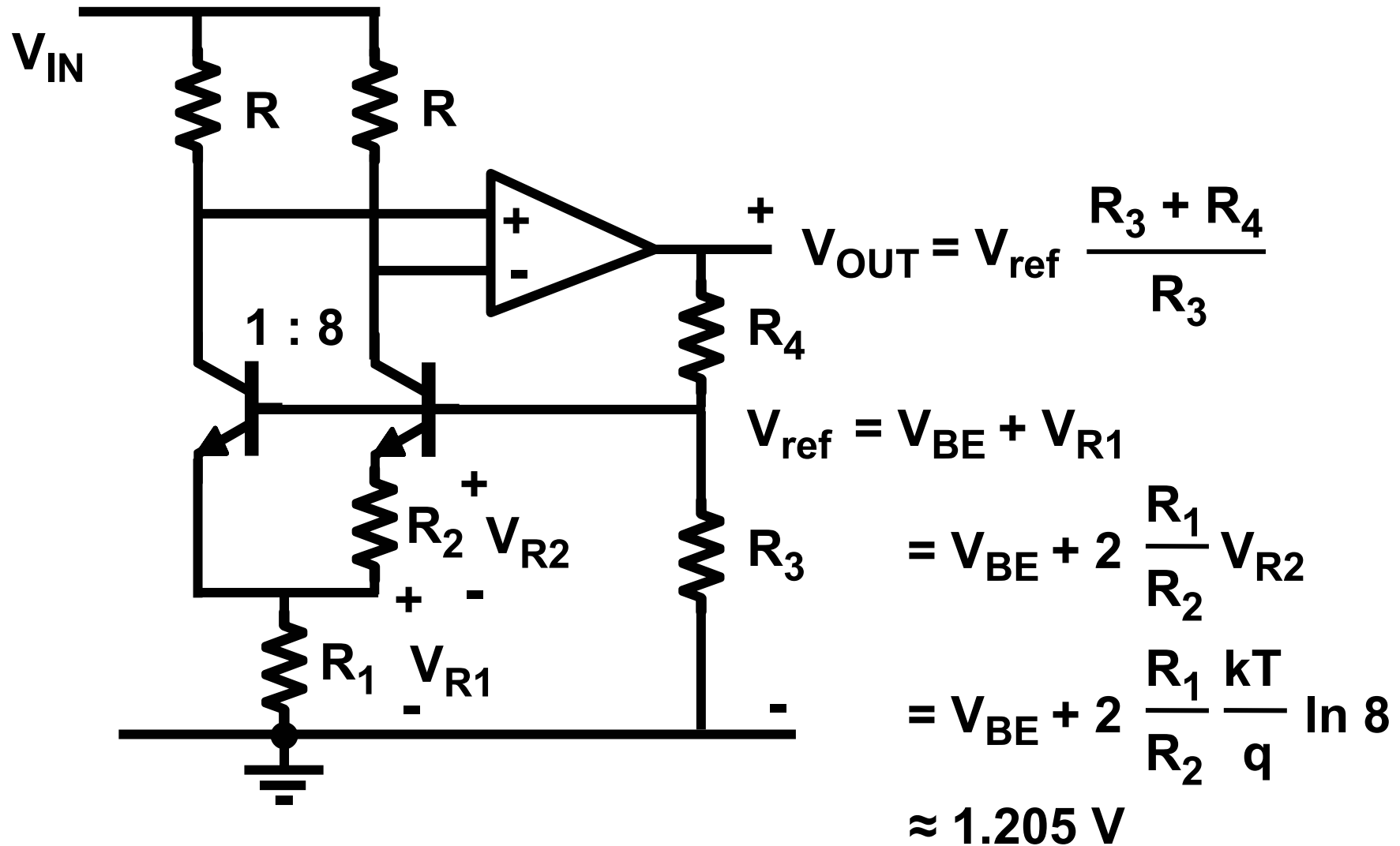
$$d[A(V_{\text{BE1}} - V_{\text{BE2}})] =$$

$$= A \frac{kT}{q} \ln n \left( \frac{dA}{A} + \frac{1}{\ln n} \frac{dn}{n} \right)$$

is PTAT !

$$= 600 \text{ mV} (1 \% + 0.46 \cdot 2\%) \approx 11 \text{ mV} \Rightarrow 24 \text{ mV or } 2\%$$

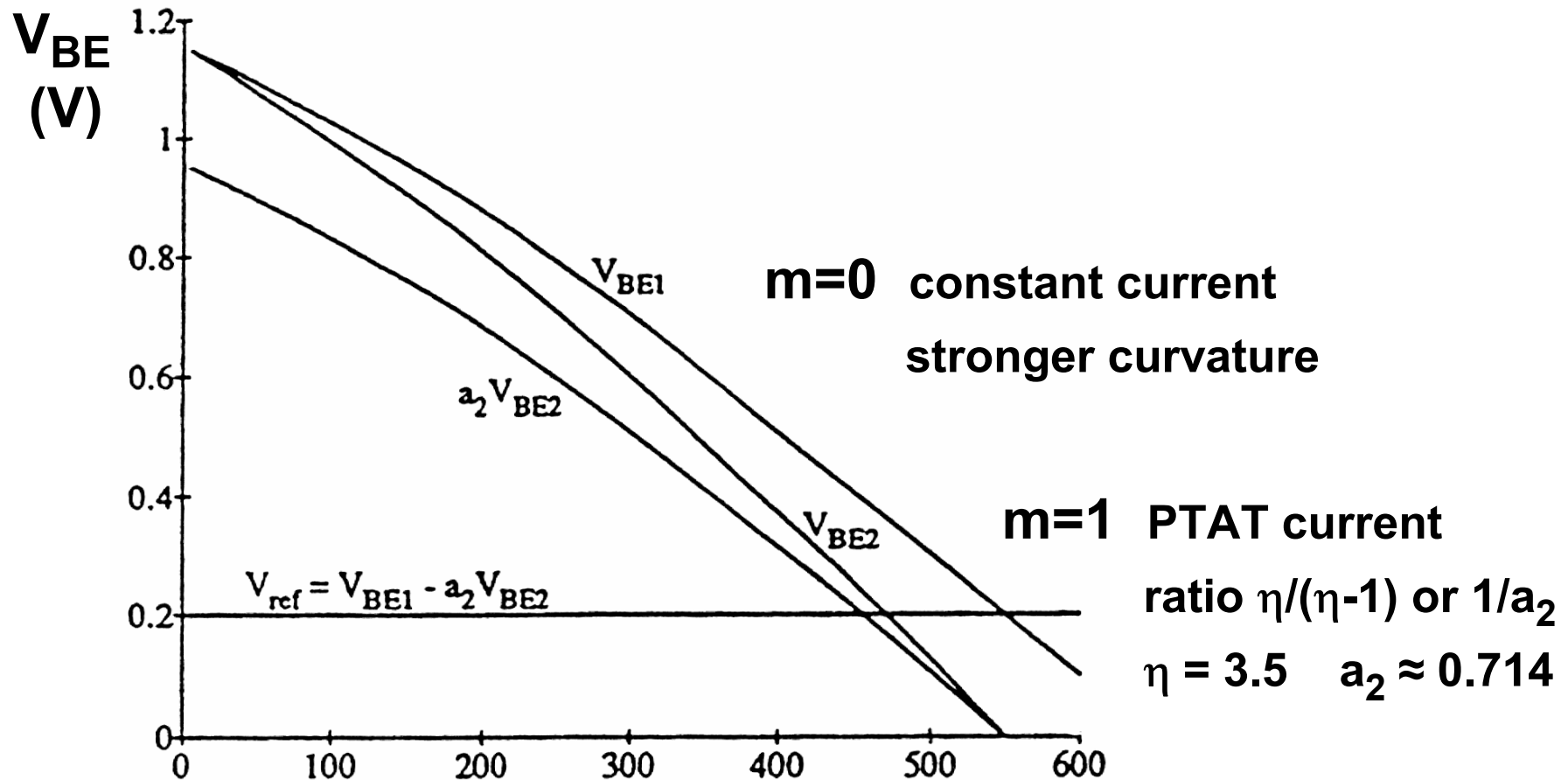
# Bipolar Bandgap reference AD580



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# Curvature correction with $\Delta V_{BE}$

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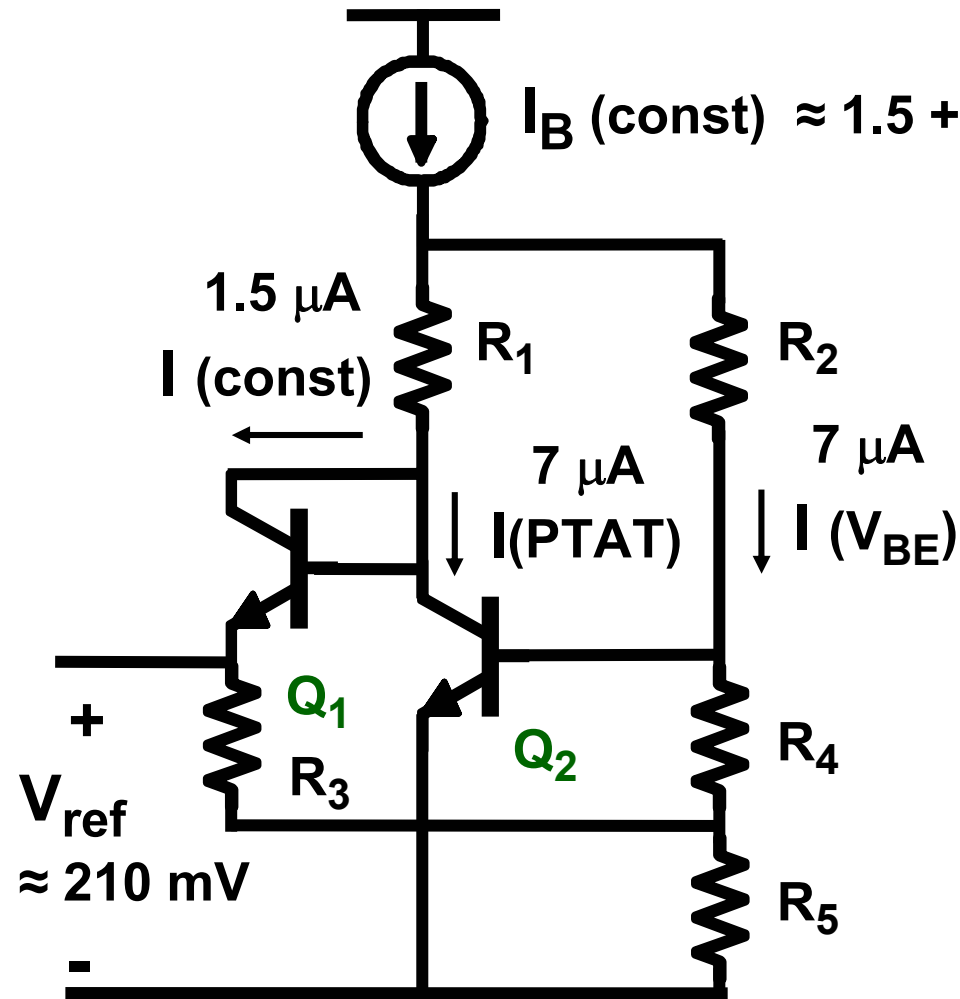


$V_{ref} \approx 210 \text{ mV}$

Ref. Widlar, Meijer, van Staveren



# Curvature correction with $\Delta V_{BE}$

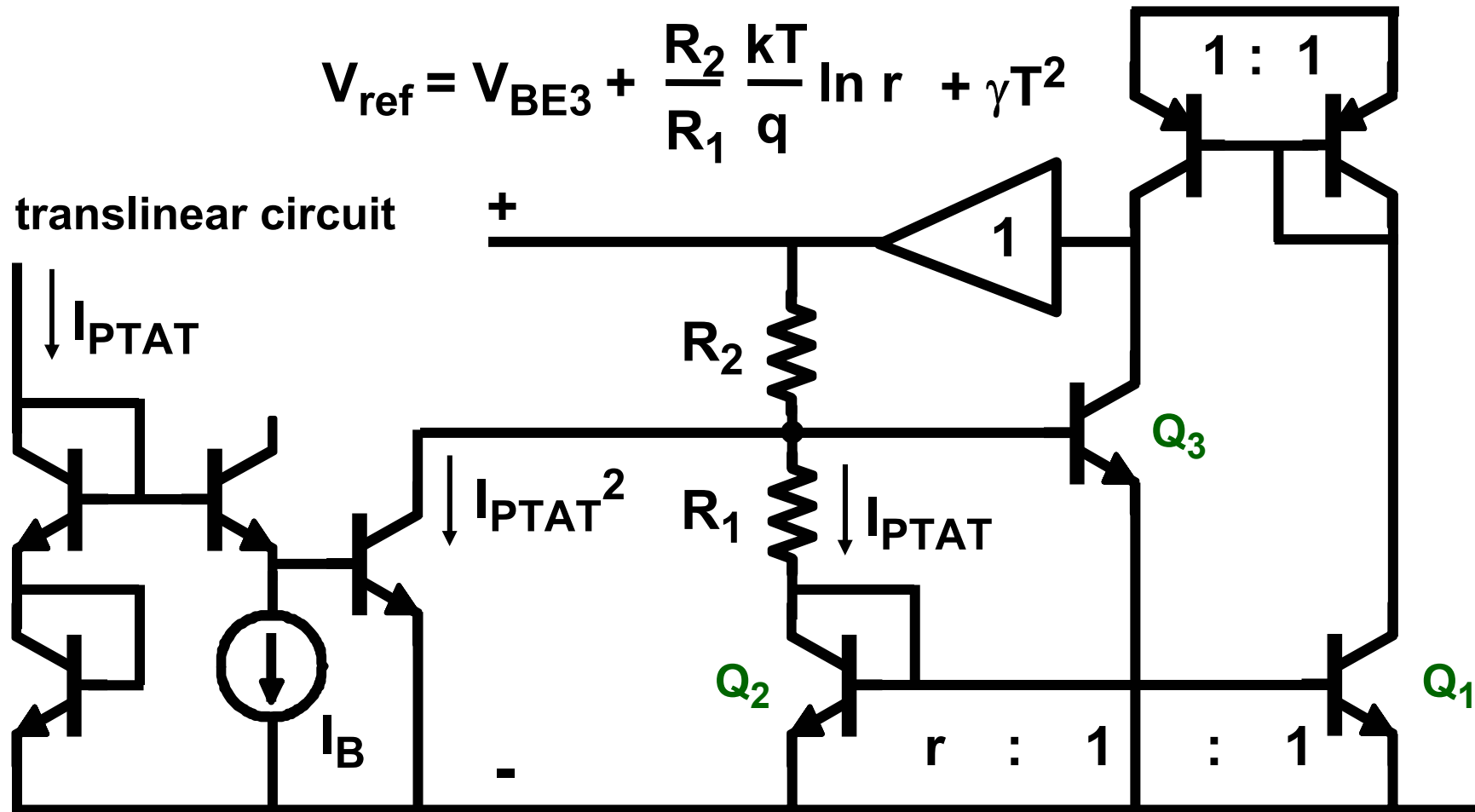


$$\begin{aligned}
 V_{\text{ref}} &= V_{\text{BE2}} + R_2 I (V_{\text{BE}}) \\
 &\quad - R_1 (I (\text{const}) + I (\text{PTAT})) \\
 &\quad - V_{\text{BE1}} \\
 &\approx V_{\text{PTAT}} + A V_{\text{BE2}}
 \end{aligned}$$

Ref. Widlar JSSC Dec.78, 838-846

# Curvature correction with PTAT2

$$V_{\text{ref}} = V_{\text{BE3}} + \frac{R_2}{R_1} \frac{kT}{q} \ln r + \gamma T^2$$



**Ref. Song JSSC Dec.83, 634-643, Degrauwe ISSCC Febr.85, 142-143**

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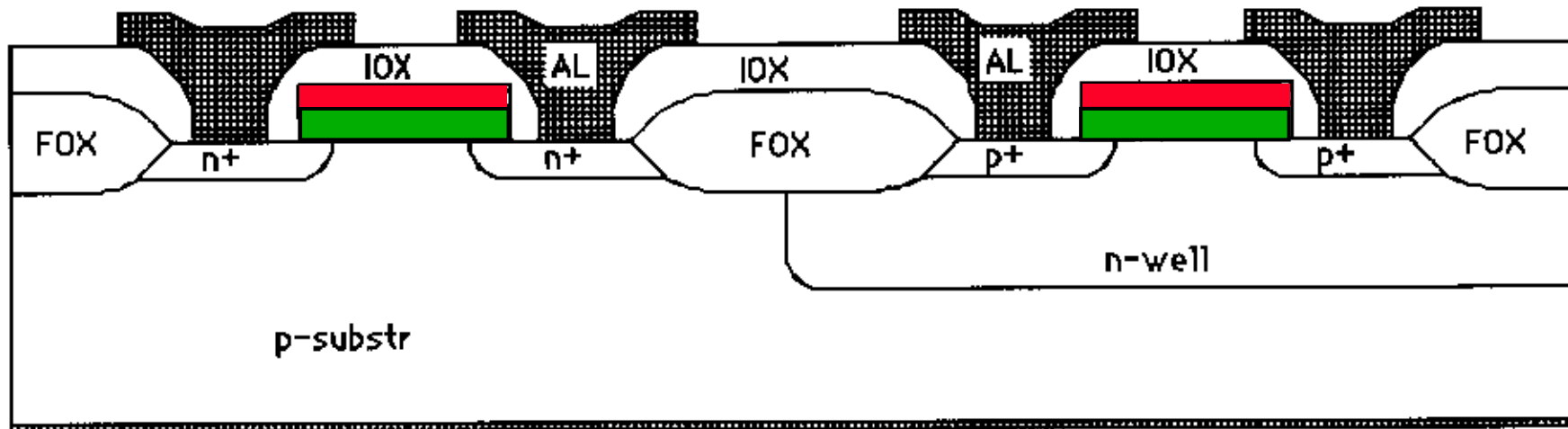
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- Bandgap references  $< 1\text{ V}$
- Current references
- LDO Regulators

Ref.: B.Gilbert, G.Meijer, ACD , Kluwer 1995

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# N-well CMOS technology

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Gate oxide

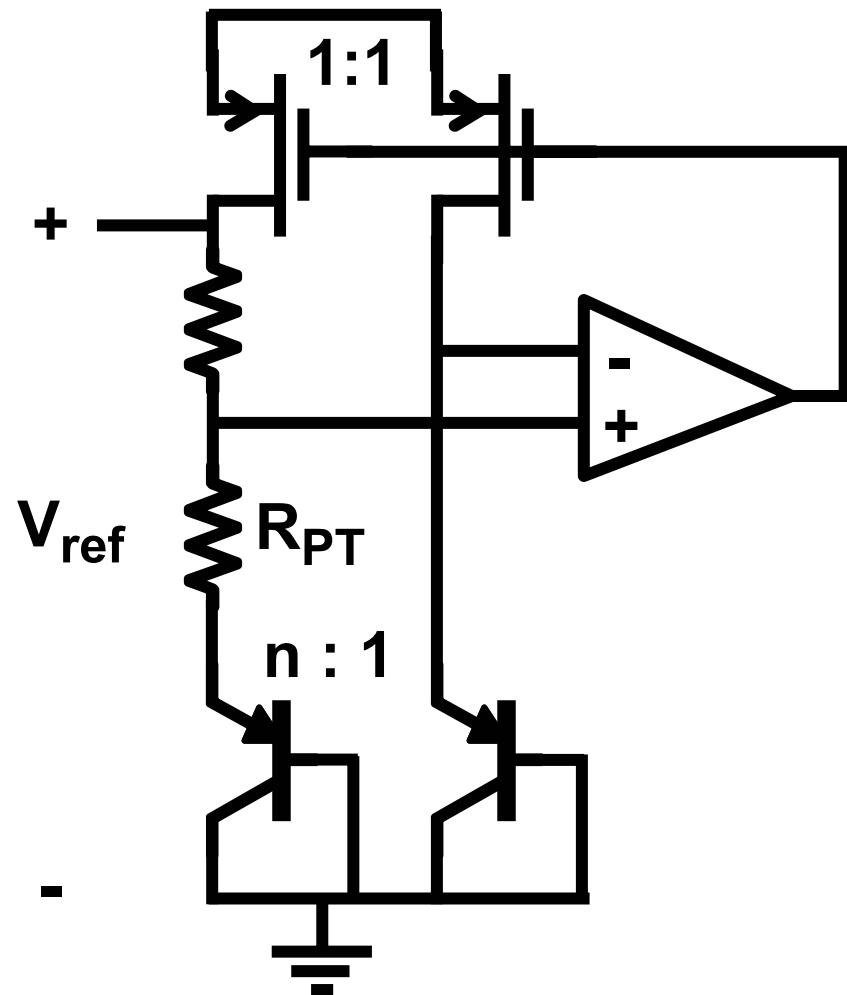
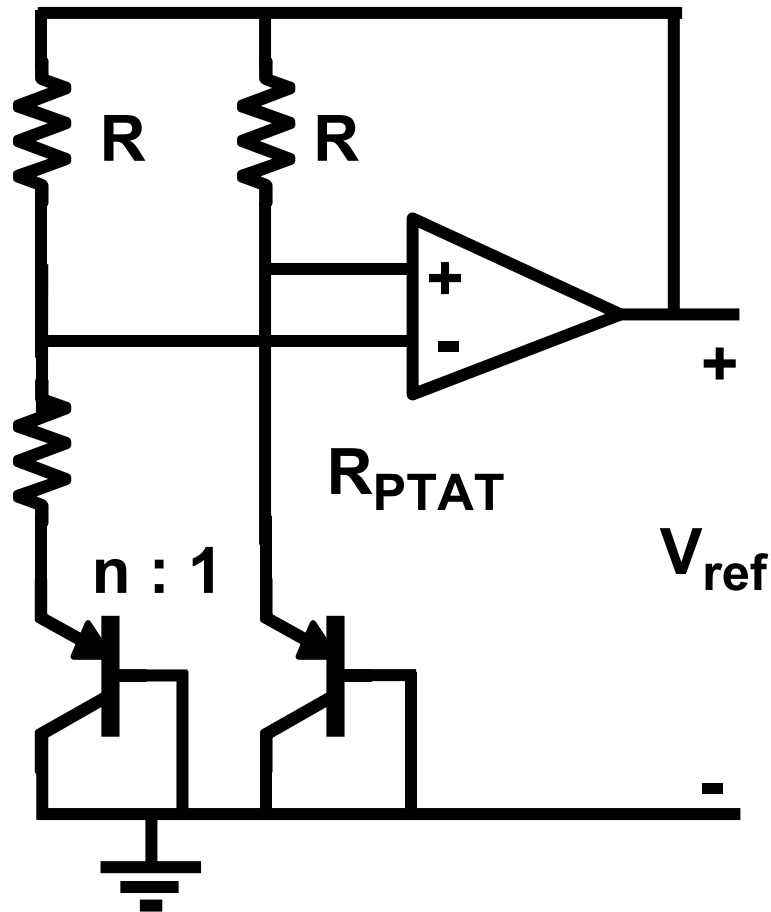


Polysilicon gate

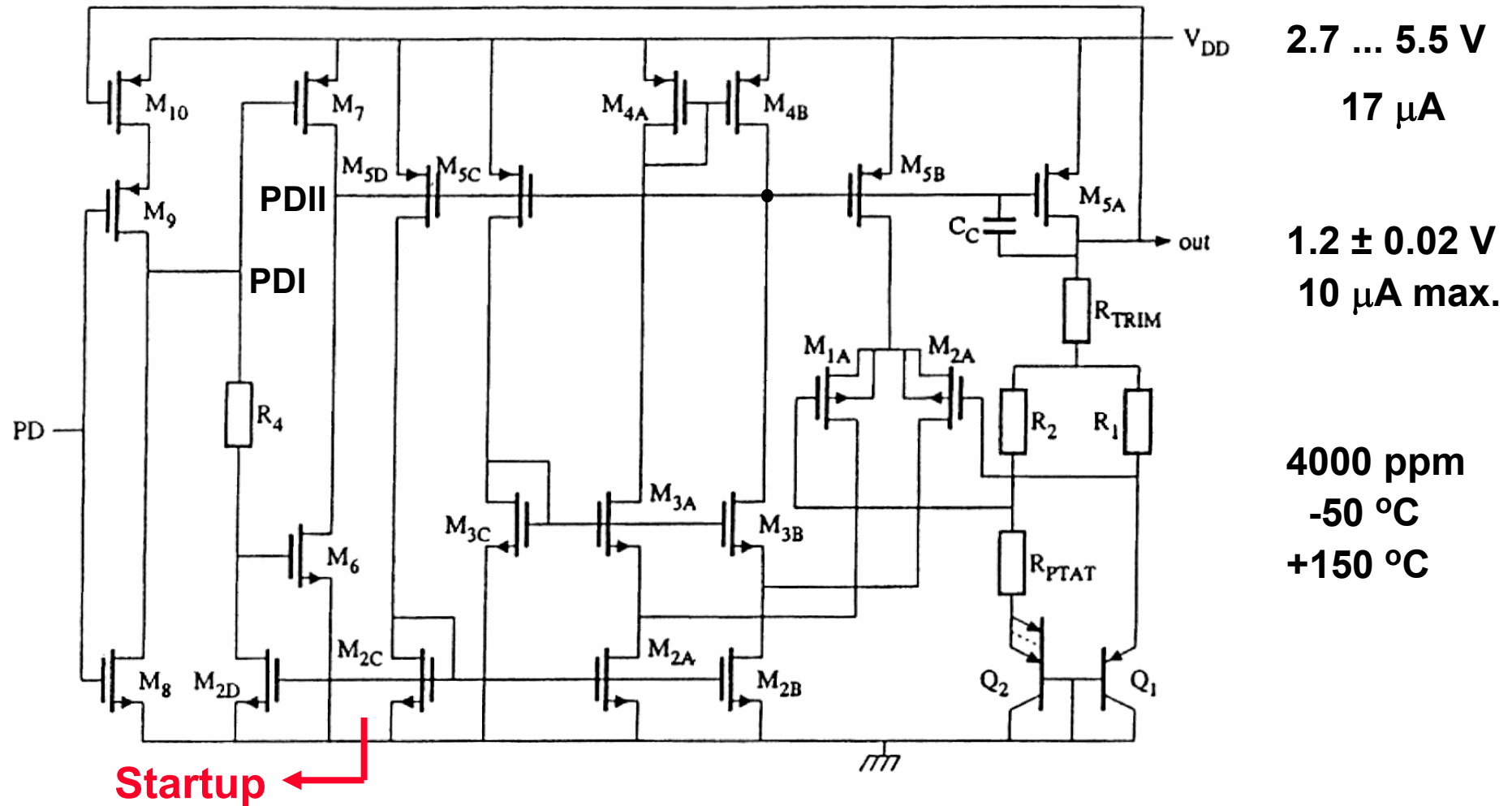
---

# CMOS Bandgap reference with opamp

---

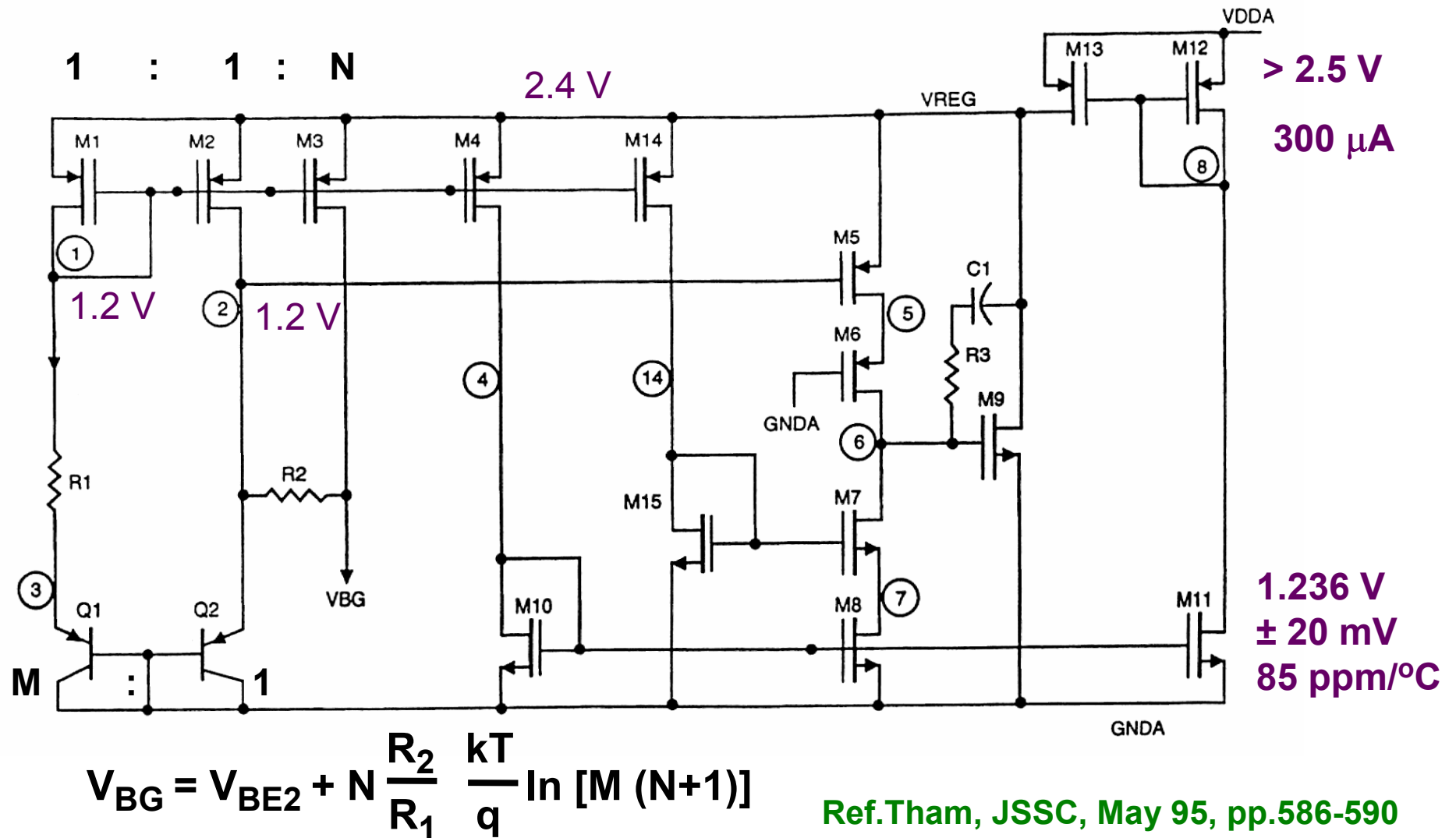


# Full CMOS bandgap reference circuit

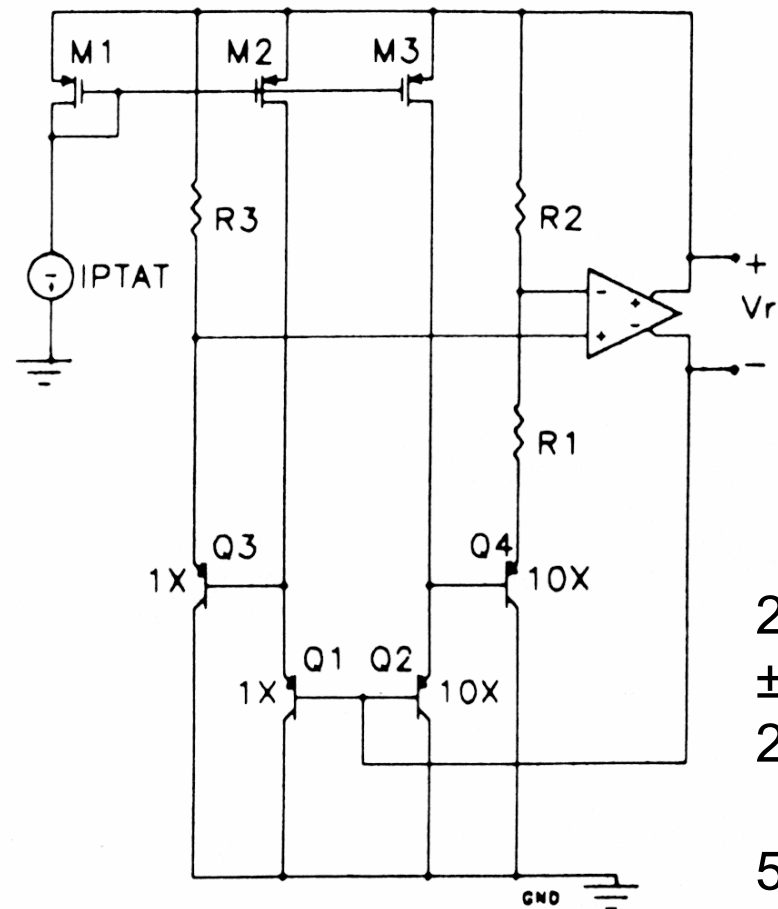
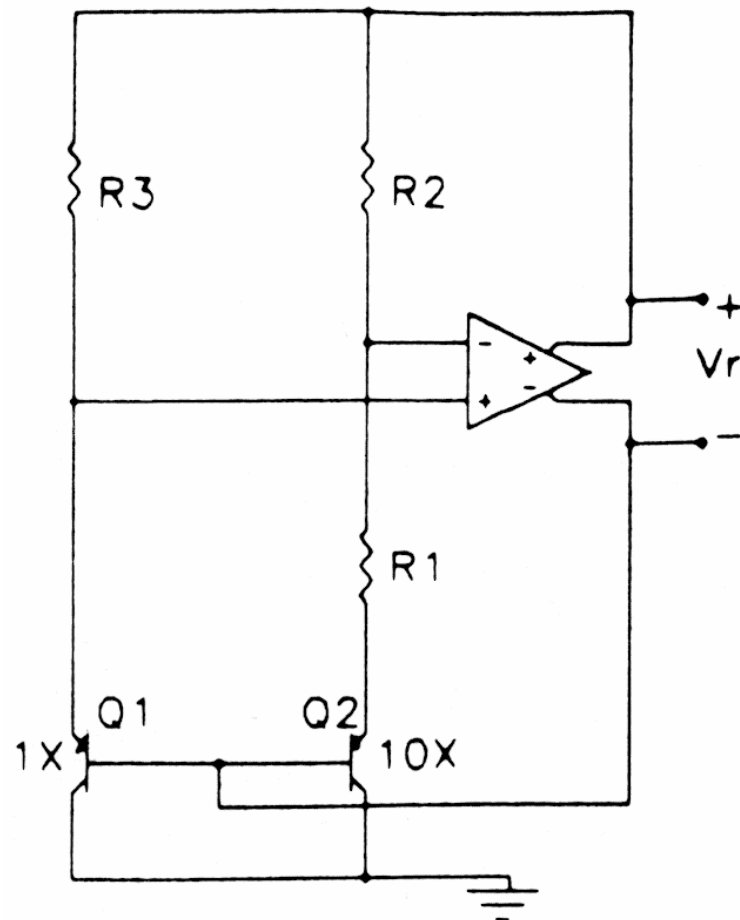


Ref. MIETEC; Meijer, ACD, Kluwer 1995

# Bandgap reference with high PSRR



# Floating CMOS bandgap reference



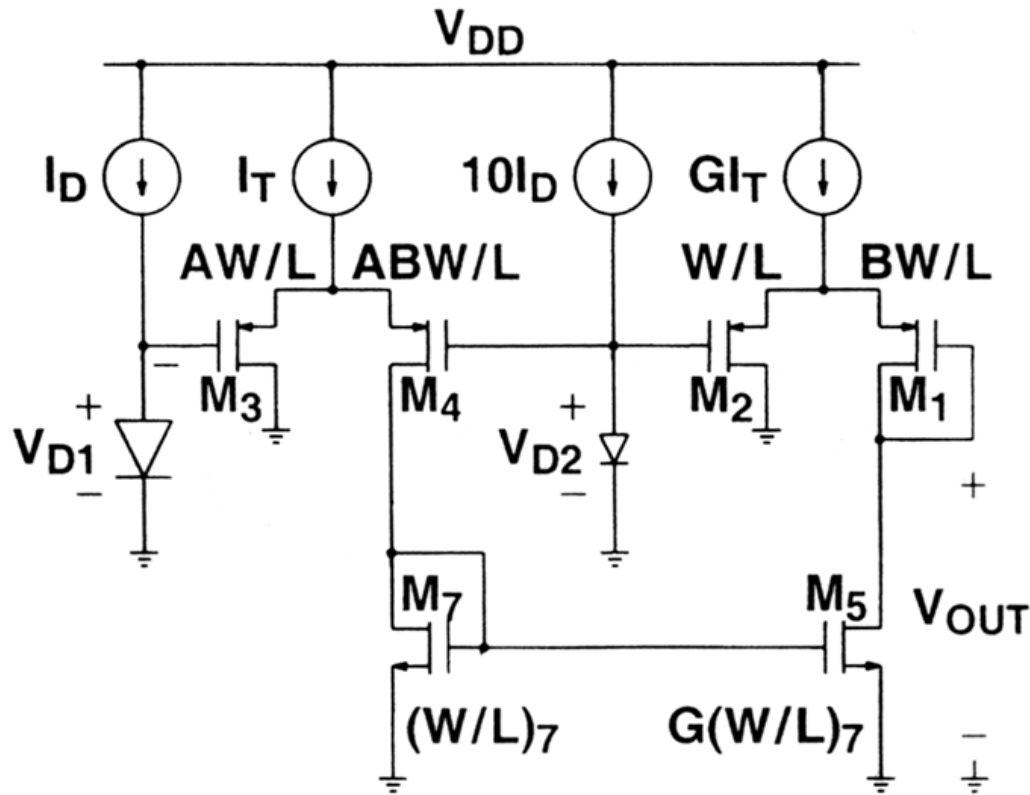
2.48 V  
 $\pm 24$  mV  
21 ppm/ $^{\circ}$ C

5 V 1.2 mA

Ref.Ferro, JSSC, June 89, pp.690-697



# CMOS Bandgap without resistors



$$\Delta V_D = V_{D2} - V_{D1}$$

$$V_{OUT} = V_{D2} + AG \Delta V_D$$

$$V_{OUT} \approx 1.12 \text{ V}$$

**9 mV 0 ...70 °C**

### 3.7 V; 0.4 mA

**A = 1.5**

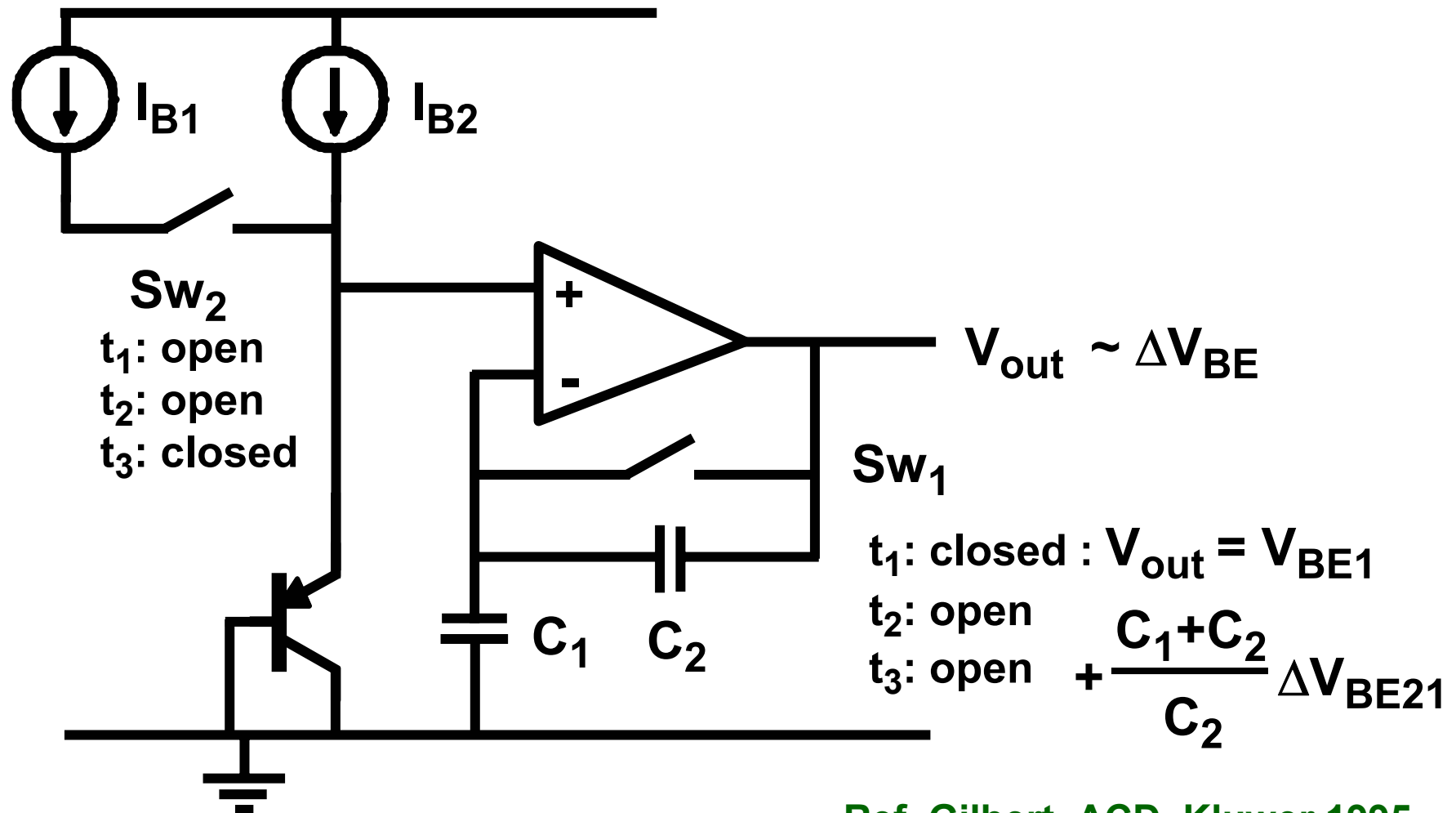
**B = 4**

**G = 6**

$$A_{D1}/A_{D2} = 8$$

**Ref.: Buck, JSSC Jan. 2002, 81-83**

# Single-junction CMOS Bandgap reference

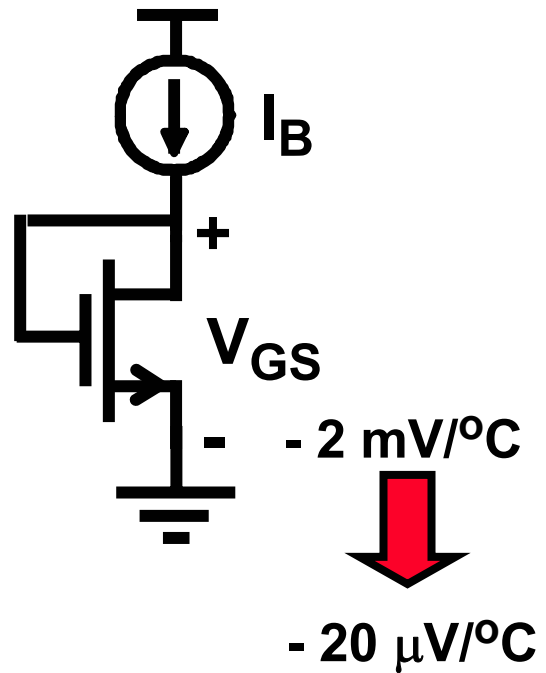


Ref. Gilbert, ACD, Kluwer 1995

---

# MOST in weak inversion ?

---



$$I_{DS} = I_{DS0} \exp \left( \frac{V_{GS}}{n k T / q} \right)$$

$$n = 1 + \frac{C_D}{C_{ox}}$$

$$C_D (V_{CB})$$

---

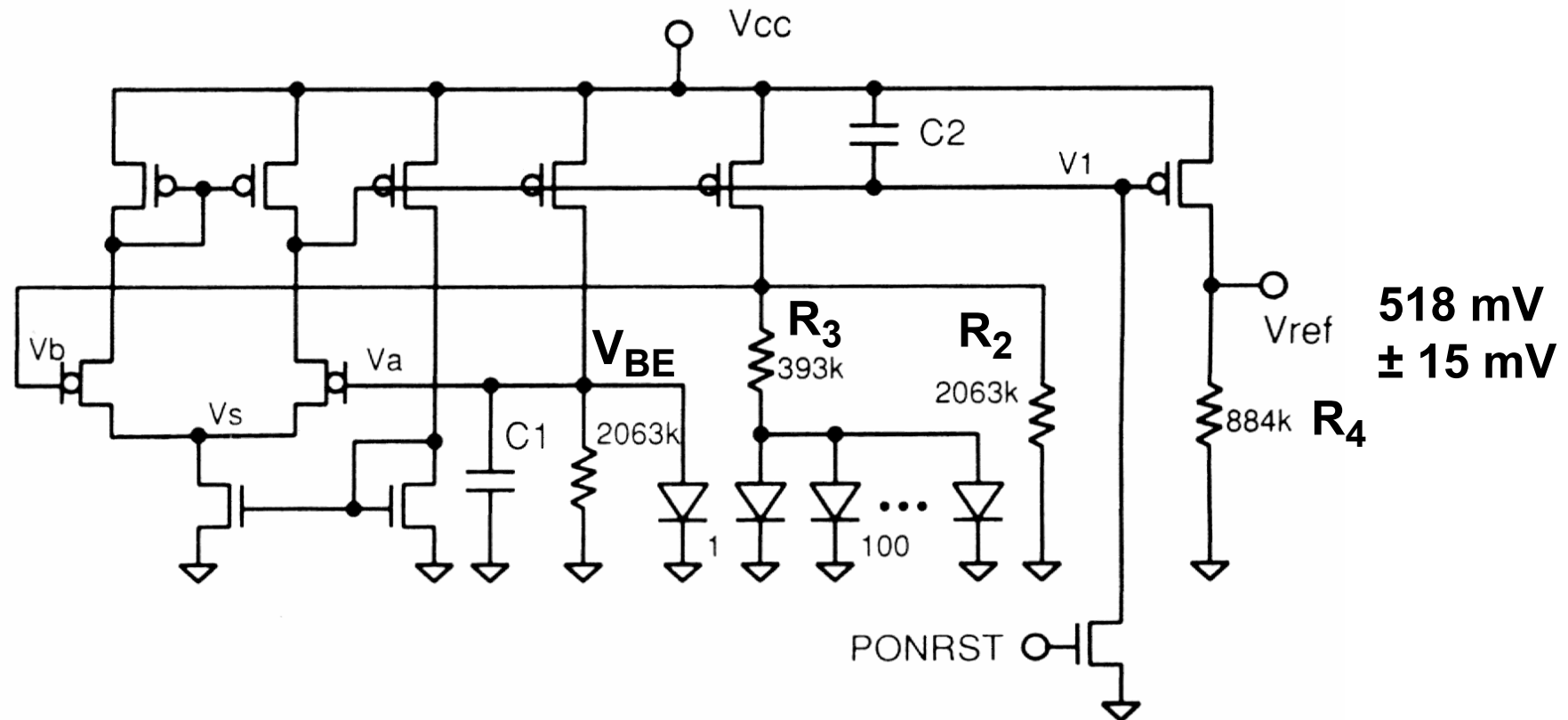
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Ref.: B. Gilbert, G.Meijer, ACD , Kluwer 1995

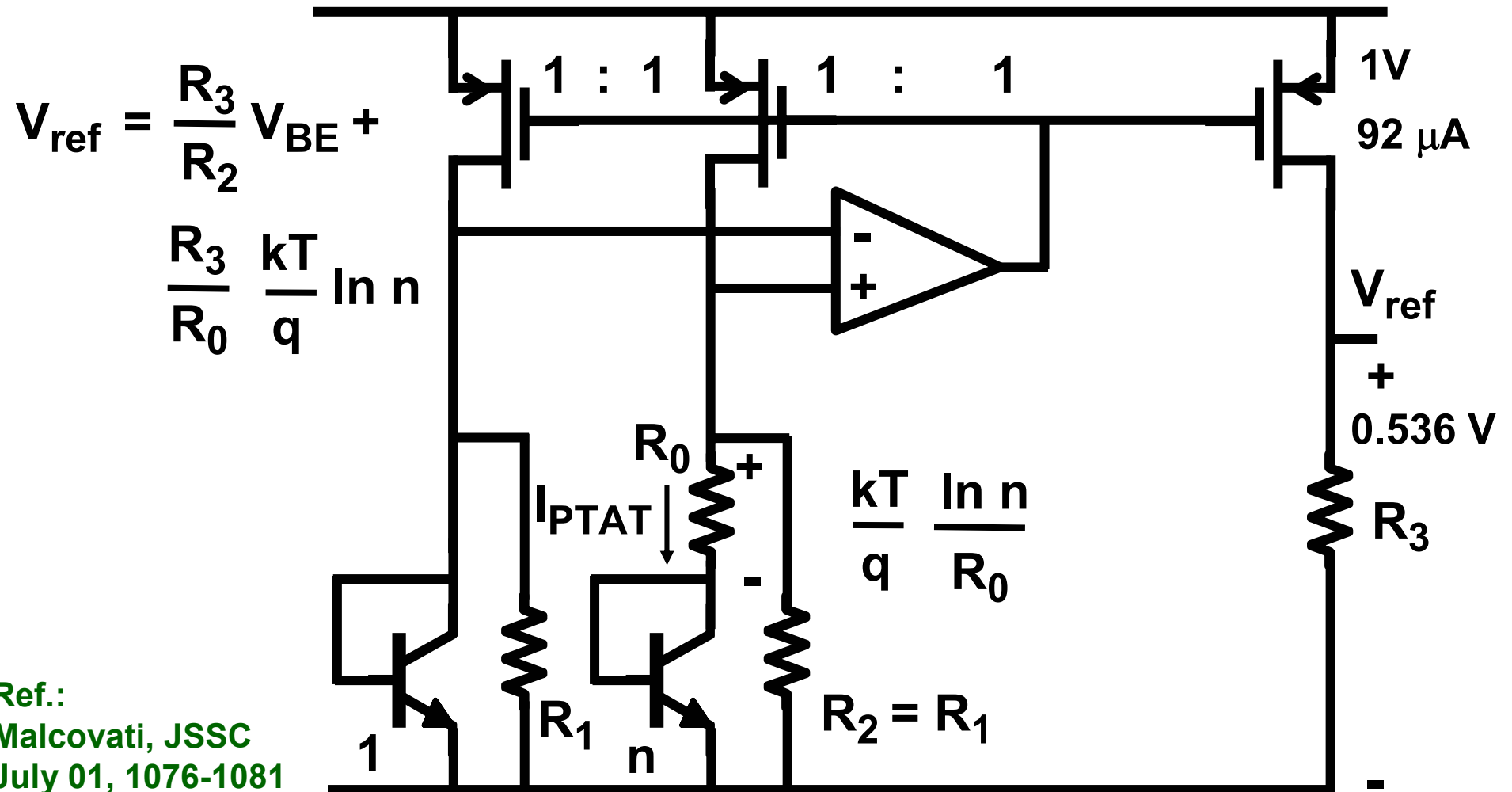
## Sub-1 V CMOS bandgap reference



$$V_{\text{ref}} = \frac{R_4}{R_2} V_{\text{BE}} + \frac{R_4}{R_3} \frac{kT}{q} \ln n \quad n = 100$$

## Banba, .., JSSC May 99, 670-673

# CMOS Bandgap with supply < 1 V

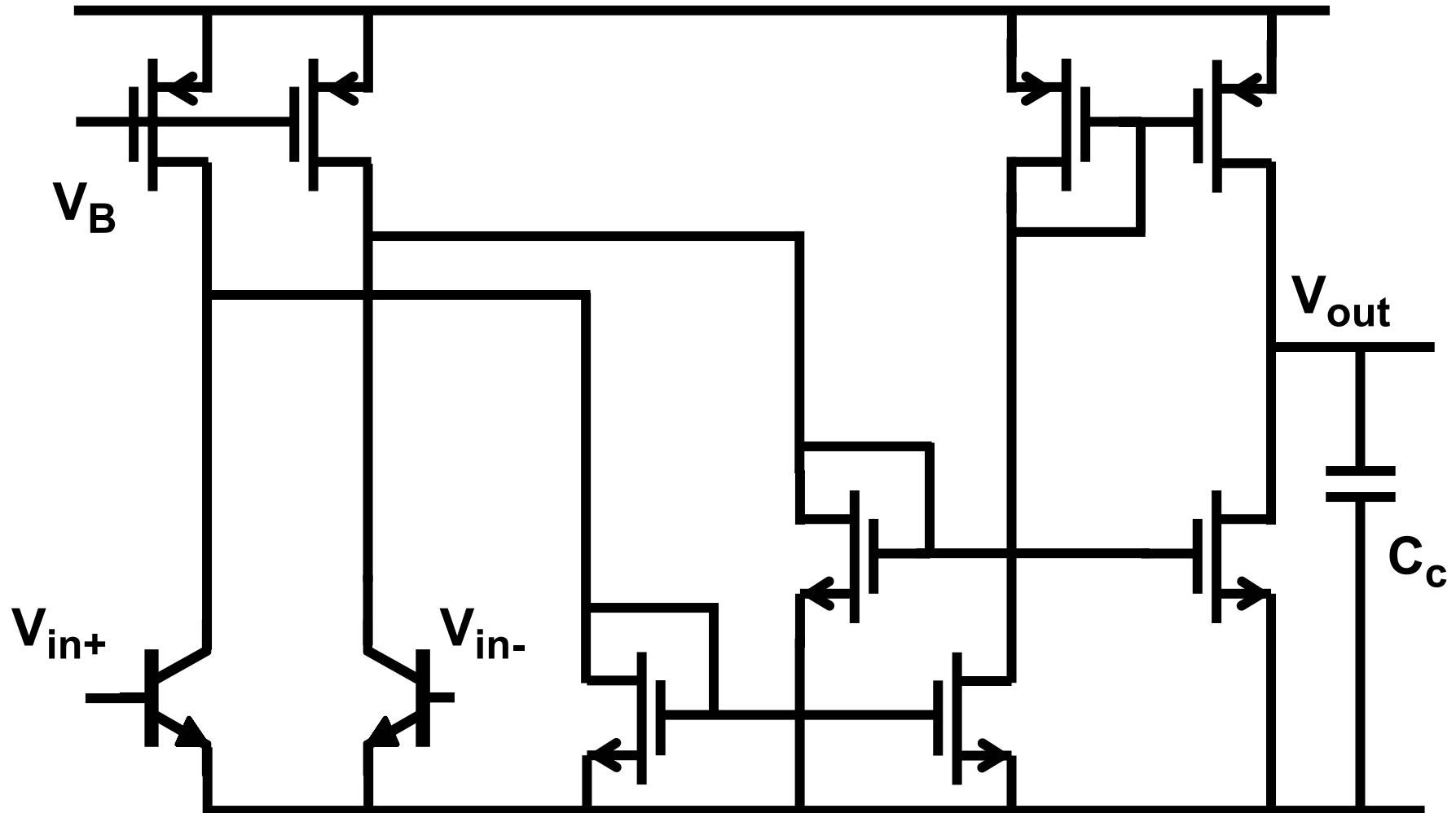


Ref.:  
Malcovati, JSSC  
July 01, 1076-1081

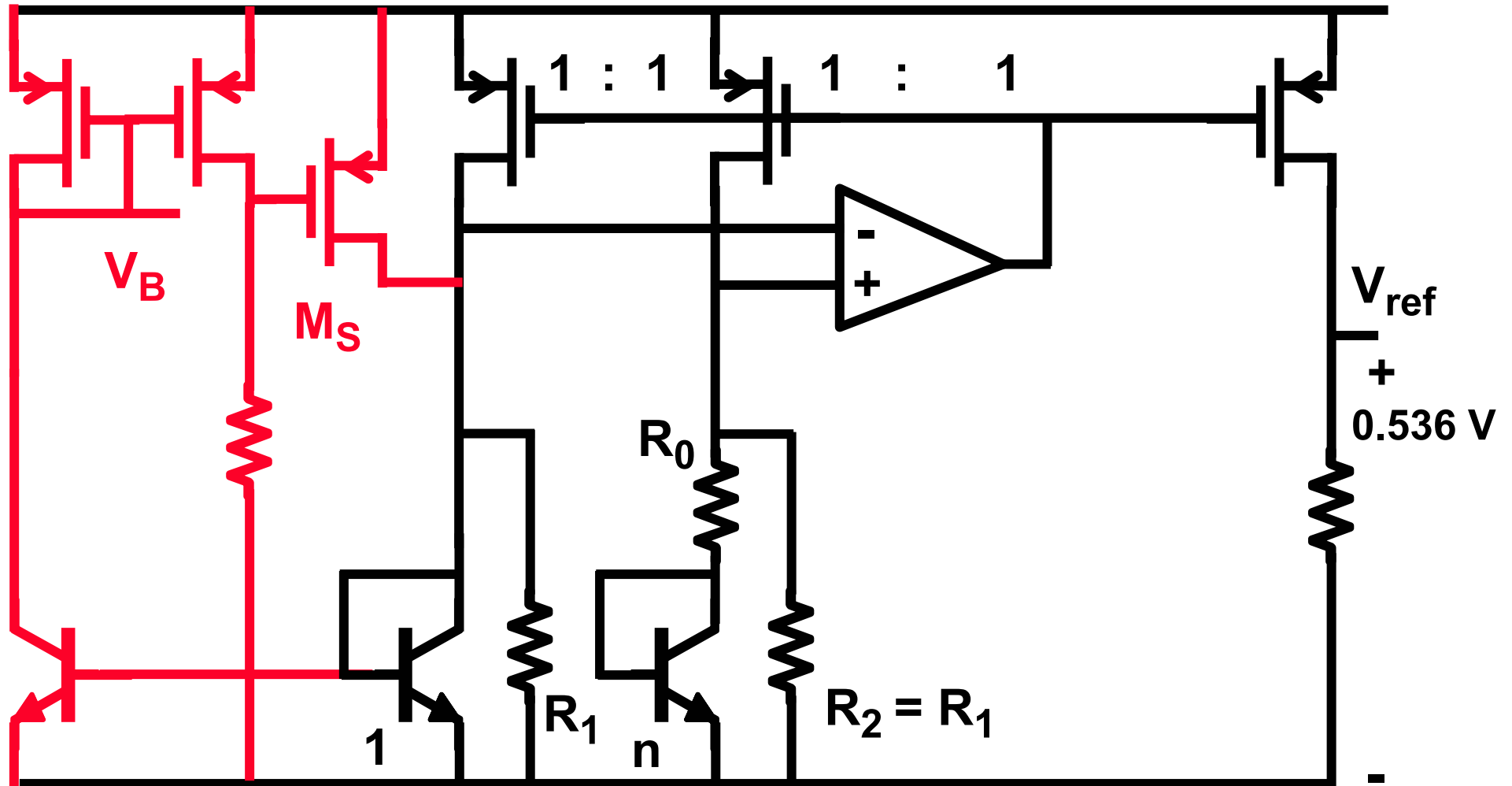
---

# 1 V opamp (1.2 MHz 25 pF 35 $\mu$ A)

---

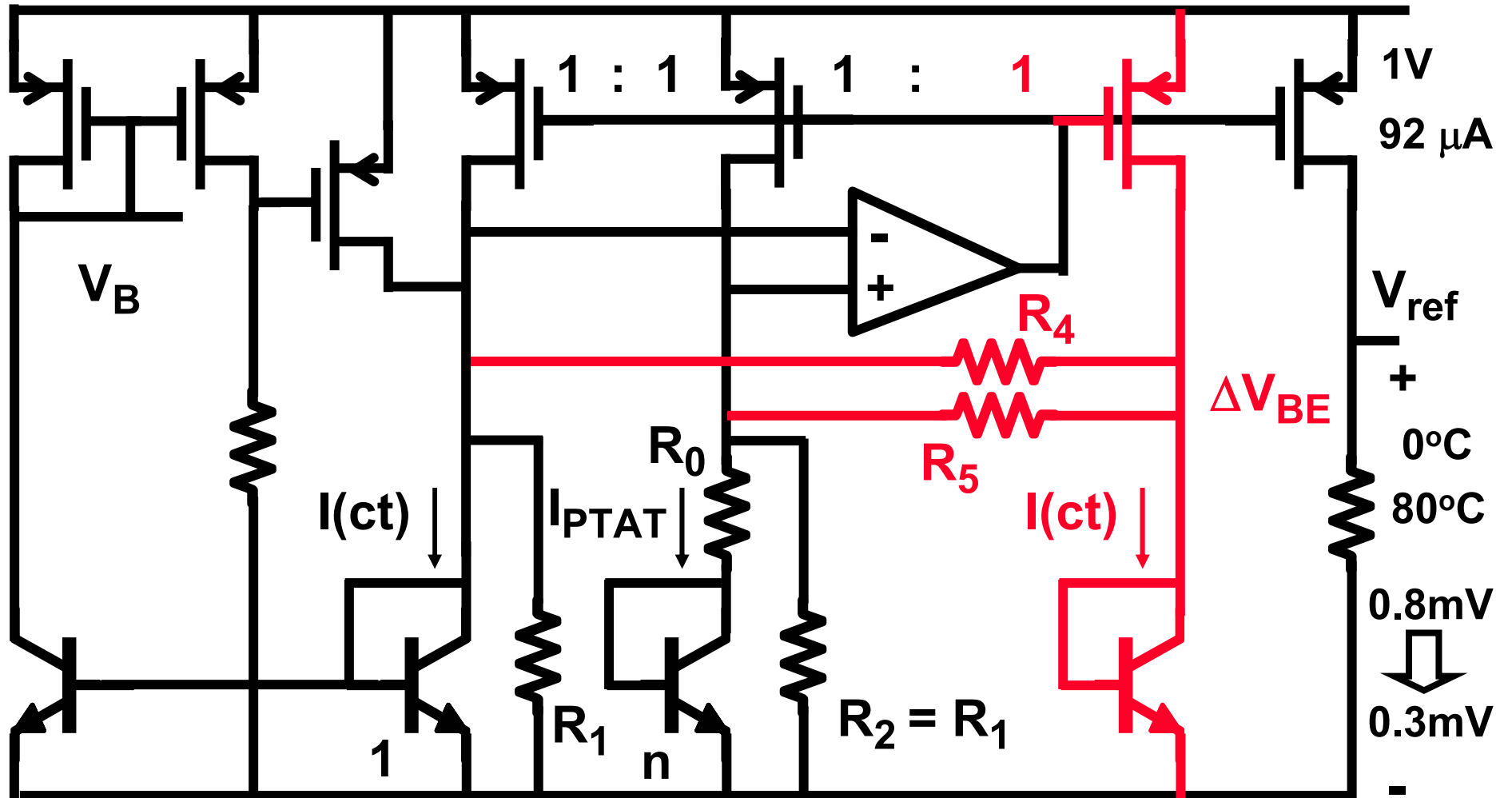


# Start-up circuit

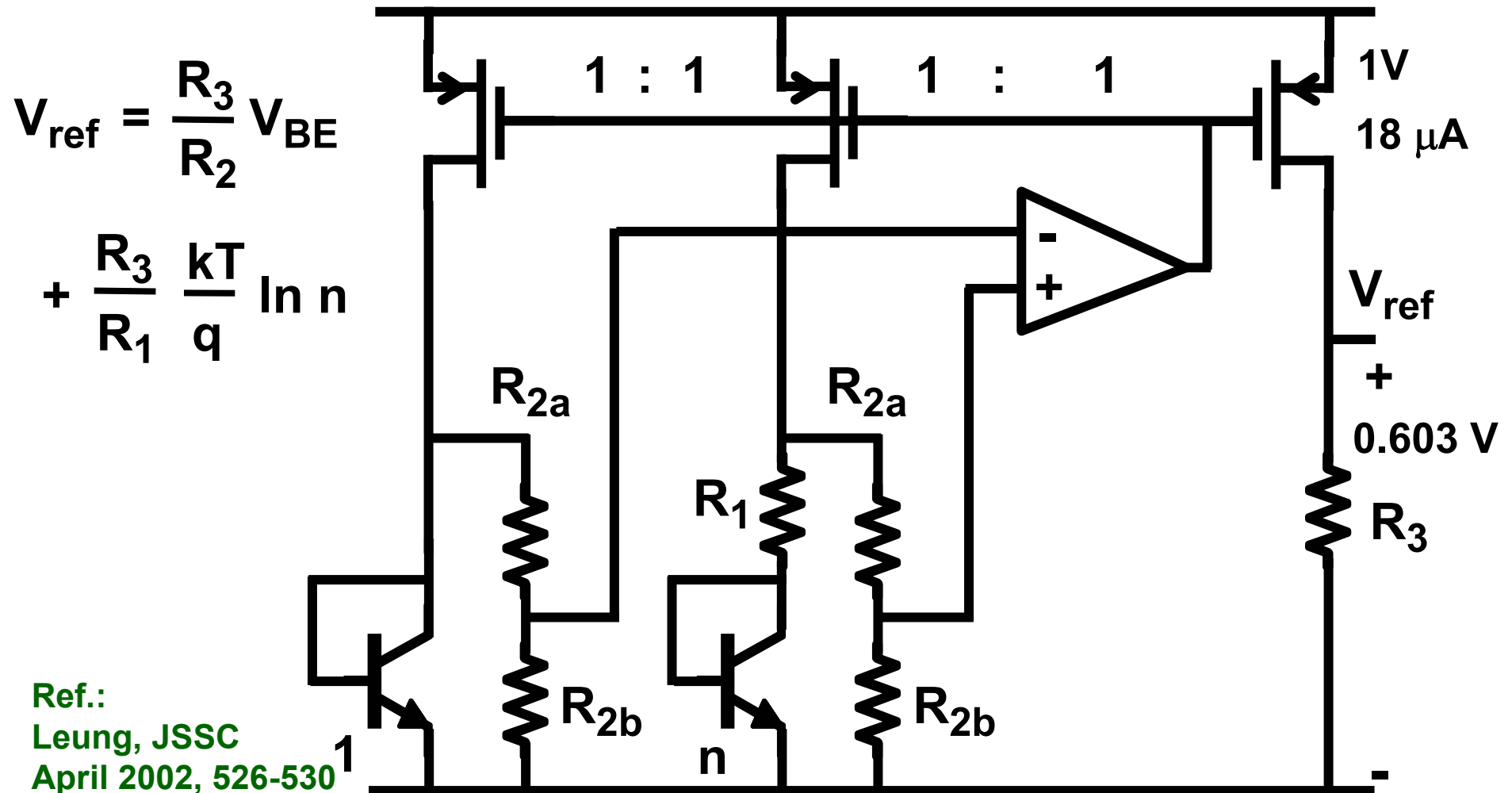




# Curvature correction



# CMOS Bandgap with supply < 1 V



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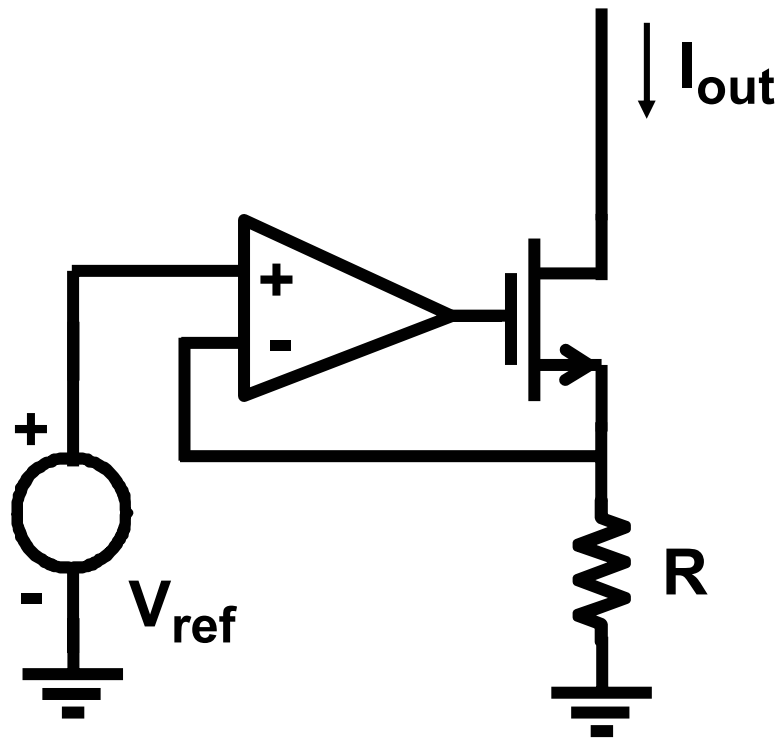
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- Current references
- LDO Regulators

Ref.: B. Gilbert, G.Meijer, ACD , Kluwer 1995

---

# Voltage-current converter

---



$$I_{out} = \frac{V_{ref}}{R}$$

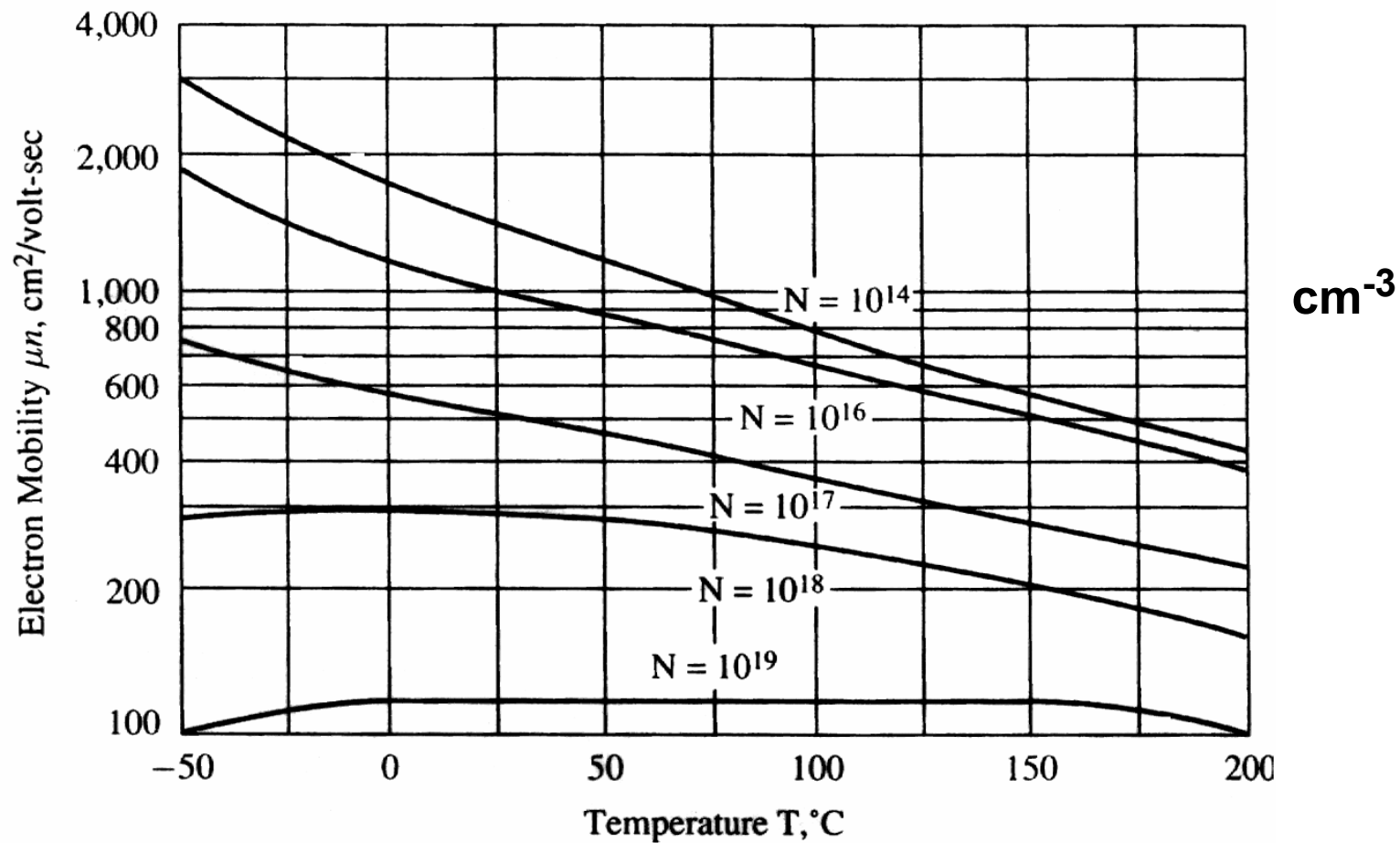
Temperature coefficient :  
depends on

$V_{ref}$   
 $R$  !

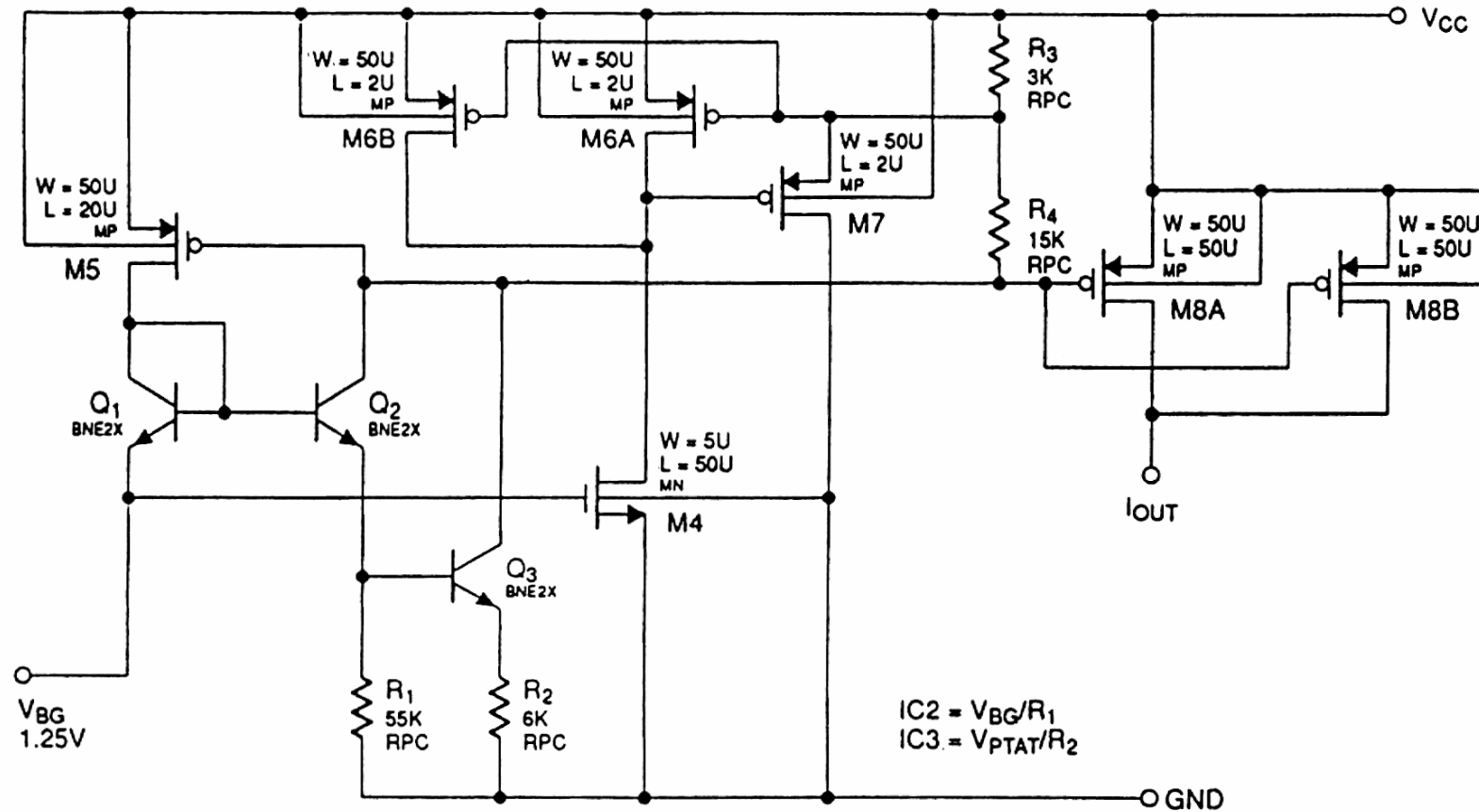
---

# Temperature coefficient of resistors

---

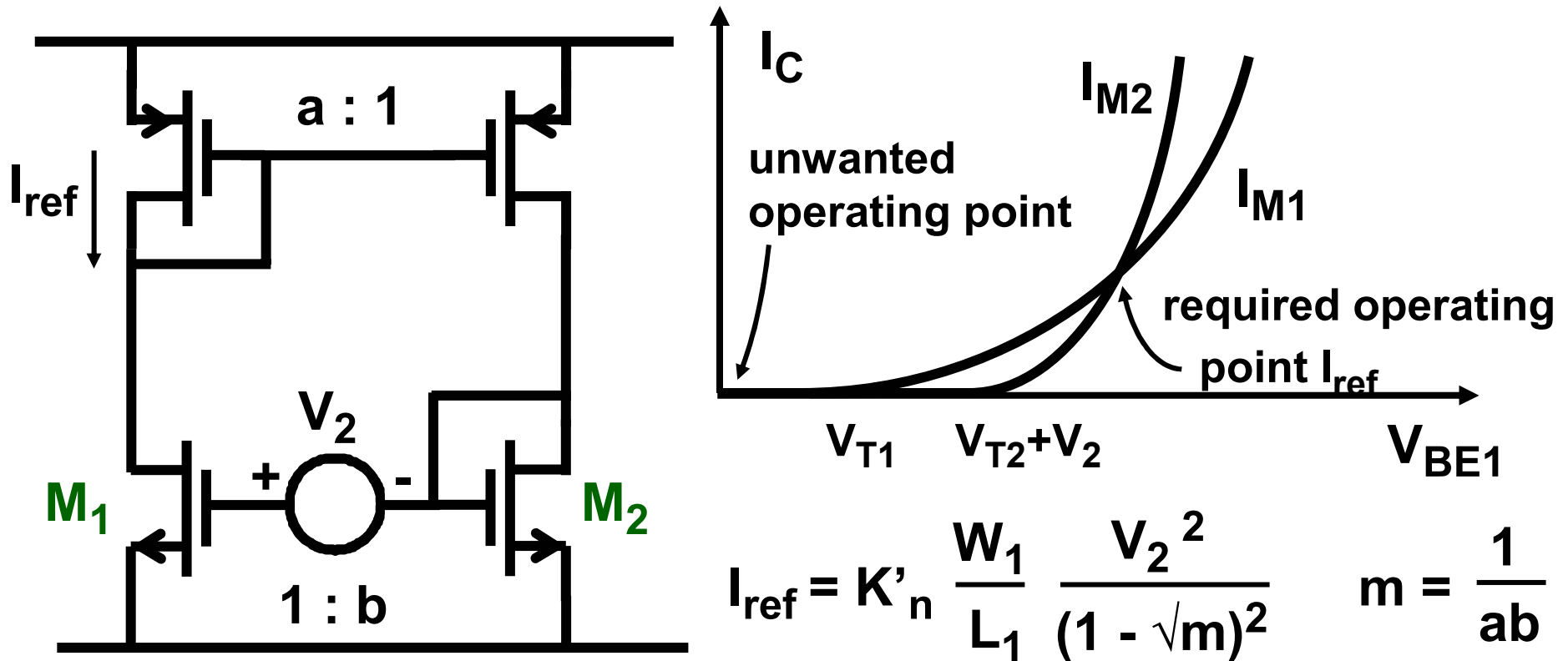


# Voltage to current converter



Blauschild, ACD Kluwer 1995

# Current reference without resistors



$$K'_n \sim T^{-1.5} \quad V_2 \sim T \quad I_{ref} \sim T^{-0.5}$$

$$V_2 \approx 0.32 \text{ V}$$

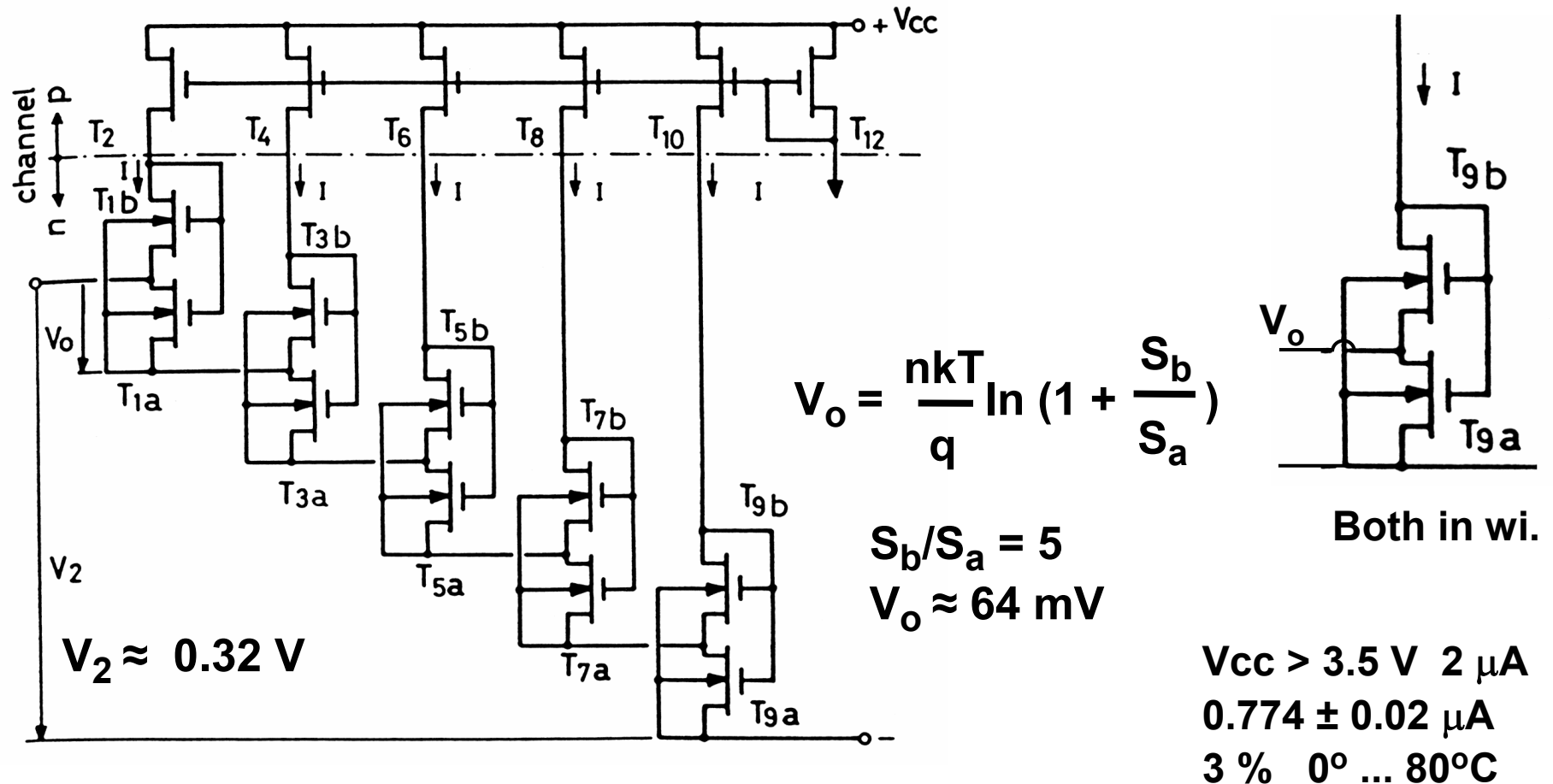
$$V_{CC} > 3.5 \text{ V} \quad 2 \mu\text{A}$$

$$0.774 \pm 0.02 \mu\text{A}$$

$$3 \% \quad 0^\circ \dots 80^\circ\text{C}$$

Ref. Op 't Eynde, JSSC June 88, pp. 821-824

# Current reference

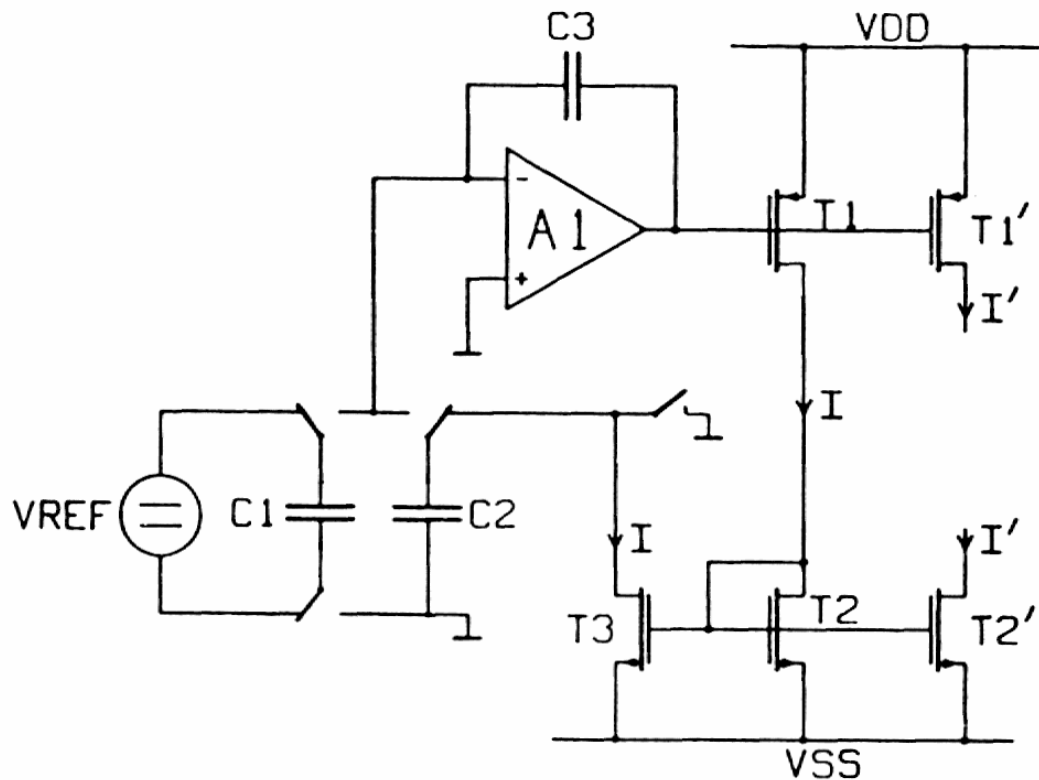


Ref. Vittoz, JSSC June 79, pp. 573-577

Ref. Op 't Eynde, JSSC June 88, pp. 821-824



# SC Voltage-current converter



$$V_{\text{ref}} C_1 = I_{\text{ref}} T_c/2$$

$$R_{\text{eff}} = \frac{1}{2f_c C_1}$$

$$I_{\text{ref}} = \frac{V_{\text{ref}}}{R_{\text{eff}}}$$

**$C_1 = C_2 = 3 \text{ pF}$      $f_c = 270 \text{ kHz}$      $\pm 5 \text{ V}$      $4 \text{ }\mu\text{A}$**

**Ref. H.Klein, W. Engl, ESSCIRC 83, pp. 119-122**

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# Table of contents

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- Principles
- Bipolar bandgap references
- CMOS bandgap references
- Bandgap references  $< 1\text{ V}$
- Current references
- LDO Regulators

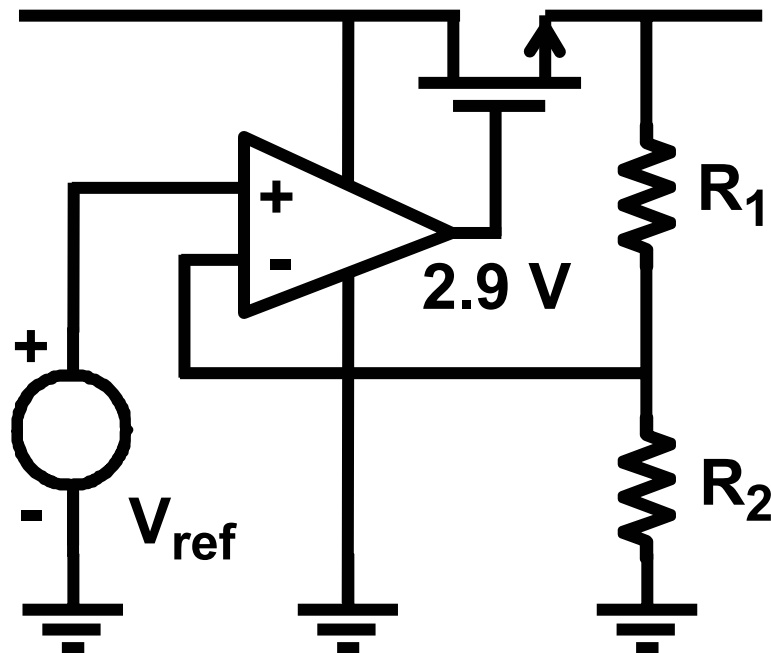
Ref.: B. Gilbert, G.Meijer, ACD , Kluwer 1995

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# Low drop-out regulator : principle

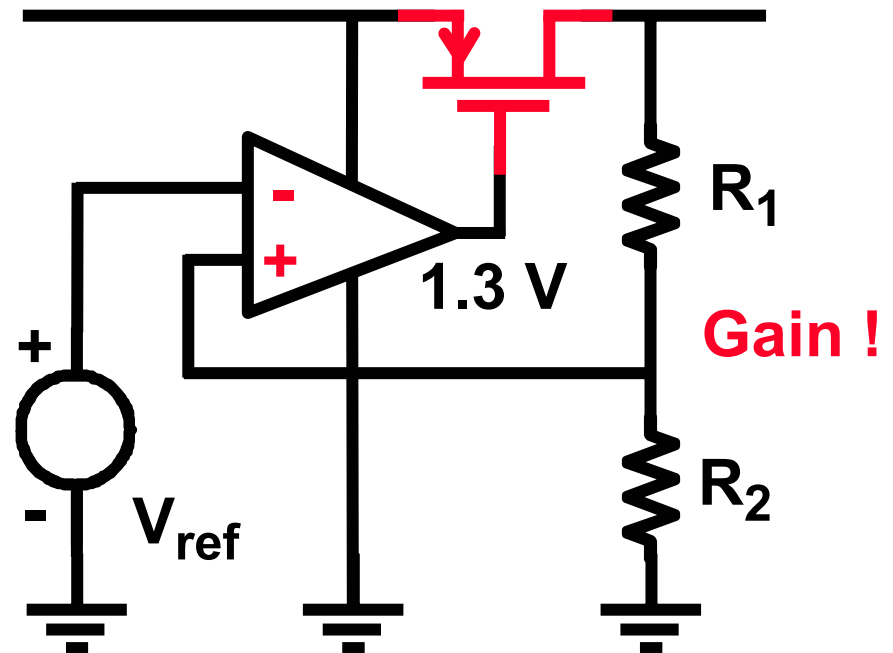
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$V_{in} = 3.1 \text{ V}$        $V_{out} = 2 \text{ V}$



$$V_{GS} \approx 0.9 \text{ V}$$

$V_{in} = 2.2 \text{ V}$        $V_{out} = 2 \text{ V}$



$$V_{out} = V_{ref} \frac{R_1 + R_2}{R_2}$$

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Ref.: B. Gilbert, G.Meijer, ACD , Kluwer 1995

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# References

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